

# Characterising MEMS: A comparison of the techniques available

**Jim Burdess, Alun Harris, John Hedley, Barry Gallacher**

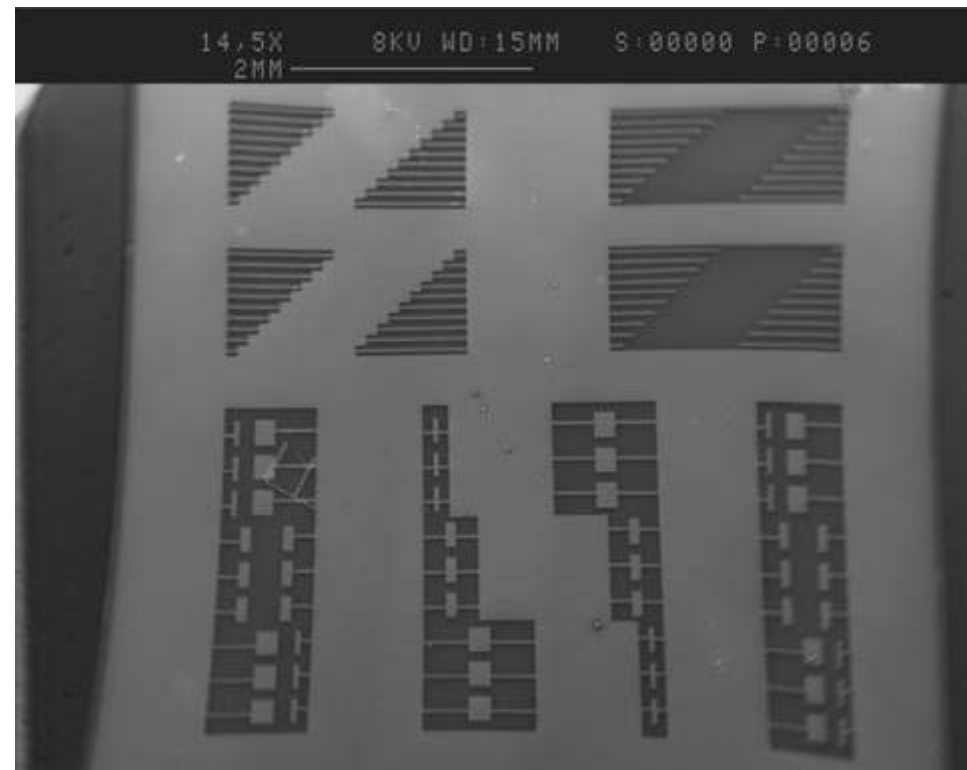


# Presentation overview

- Introduction – why characterise?
- Basic equipment
  - Mounting and actuation
  - Vibrometer, profiler, Nd:YAG laser
- Examples
  - Development of 3 axis gyroscope
  - Edinburgh University, NPL
- Further developments – Raman spectroscopy
- Summary

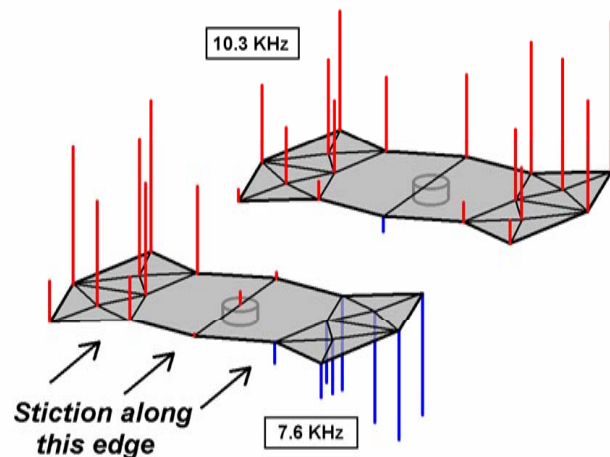
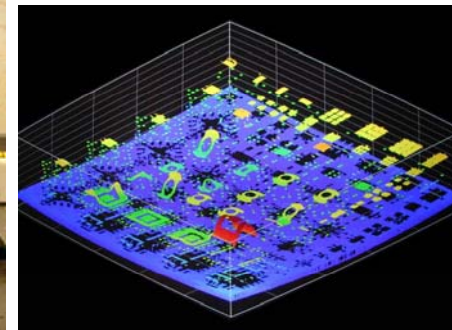
# Introduction

- Why characterise?
- Are they functional?
  - Yes – do they operate as expected (e.g. frequency)?
  - No – why not?



# Why optically characterise?

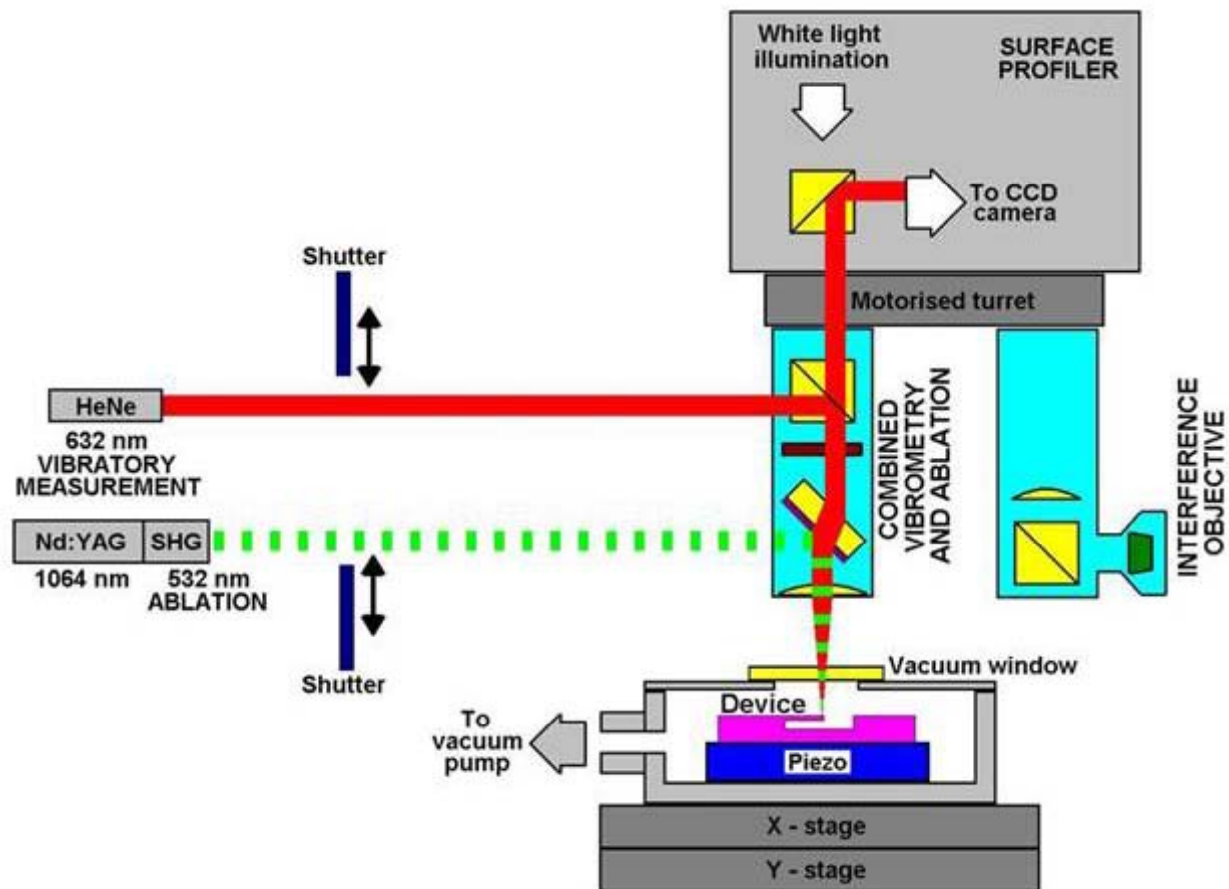
- Independent method of testing to localise fault – i.e. mechanical, electrical, etc.
- Non-contact



# The lab

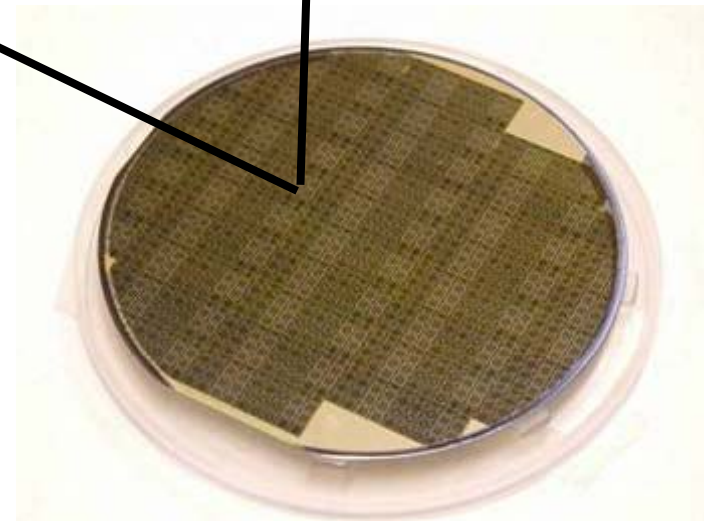
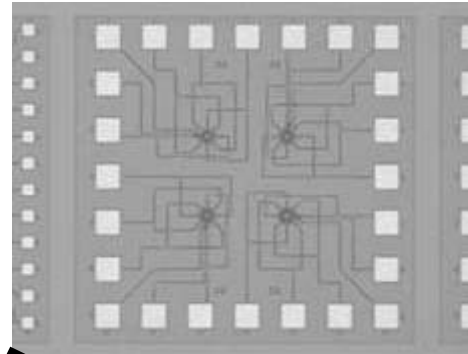


# Equipment schematic



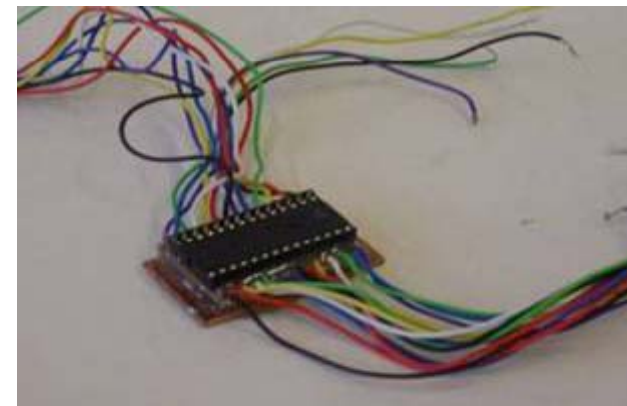
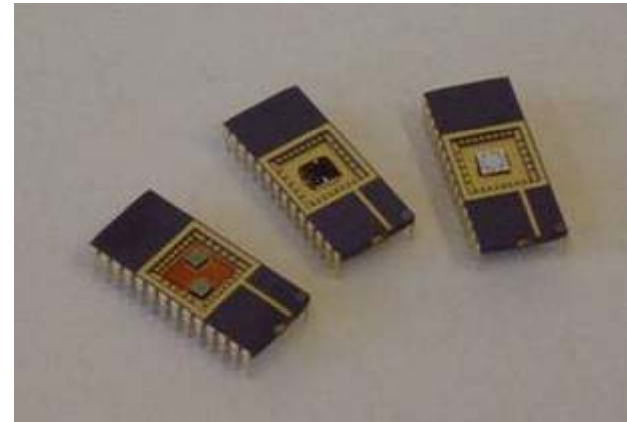
# Mounting and actuation

- Mounting requirements
  - Rigid fixing
  - Easily attached / removed
  - Operational in a vacuum
- Actuation requirements
  - Drive device without connections to wired electrodes
  - Tested under vacuum



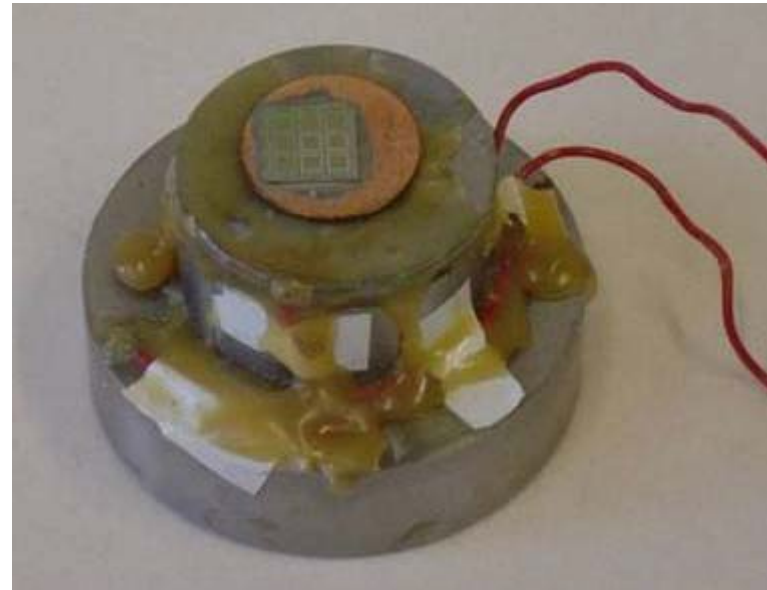
# Chip mounted

- Preprocessing
  - Photoresist as glue?
- Simple plug in
  - Less chance of device damage
- Ready for wire bonding
- Size limited! (1cm<sup>2</sup>)

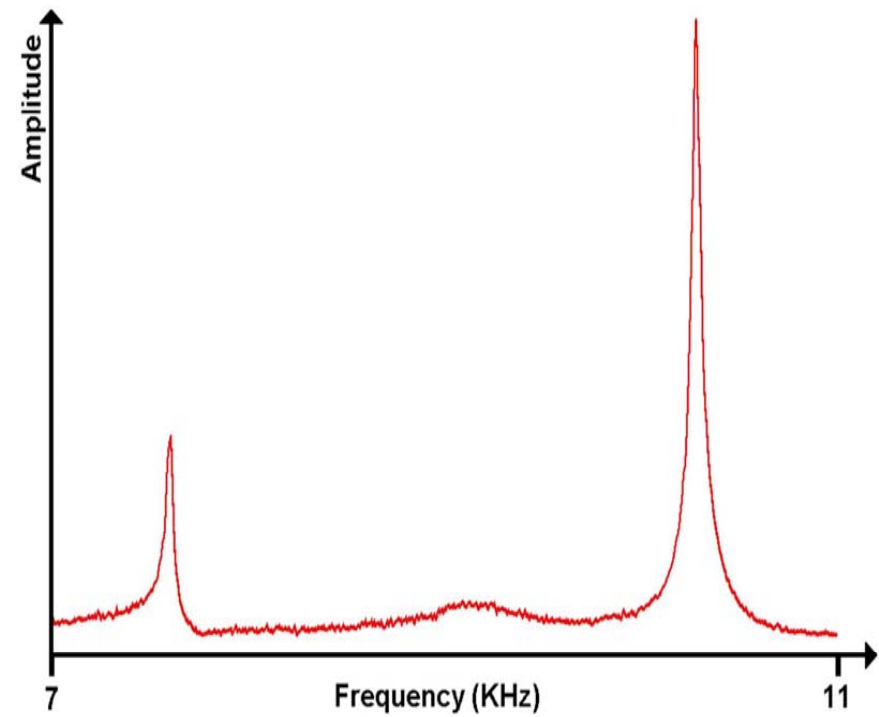
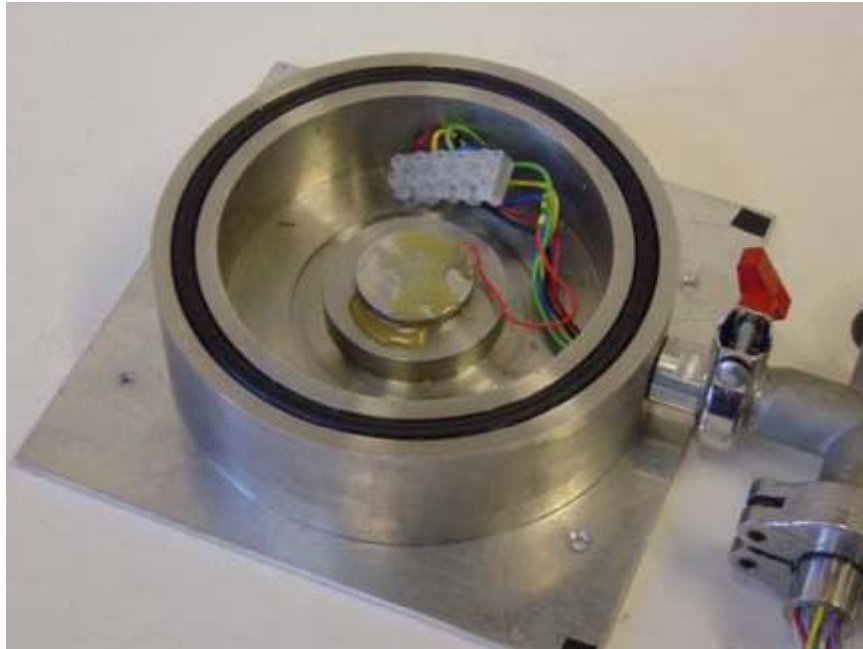


# Wax mounted

- Effective
- Quick
- Messy
- End of processing
- Copper disks



# Mechanical actuation (*piezo disk*)

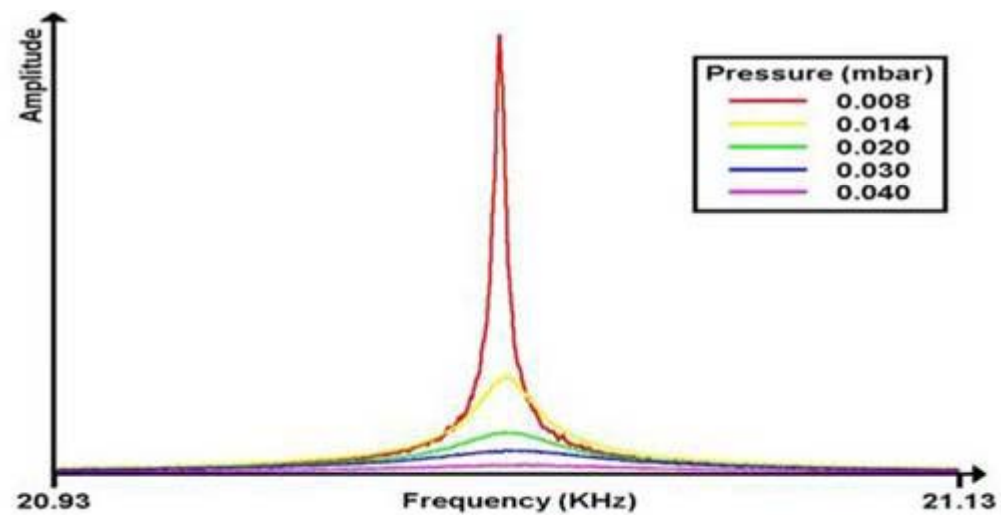
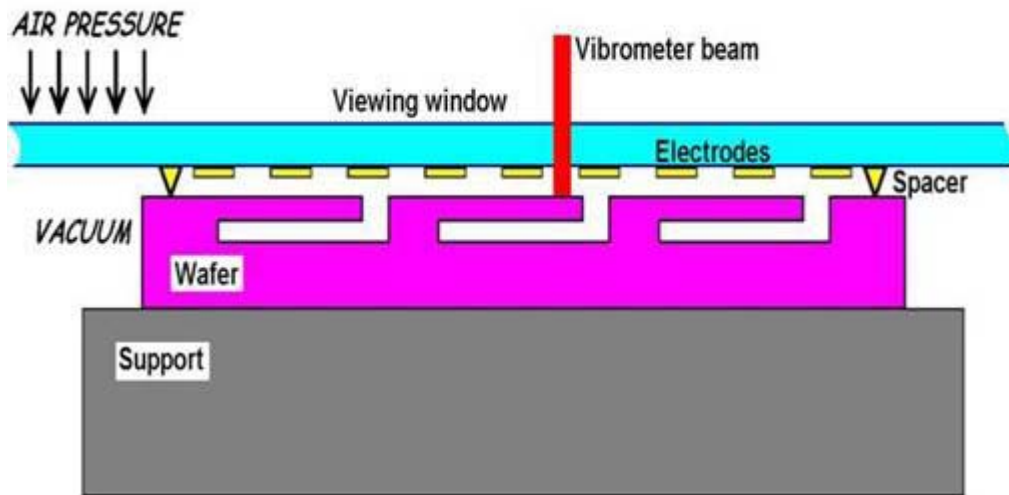


# Mounting: Pressure plate

- Larger samples (wafer)
- Spacer required
- Stresses?
- Continued processing

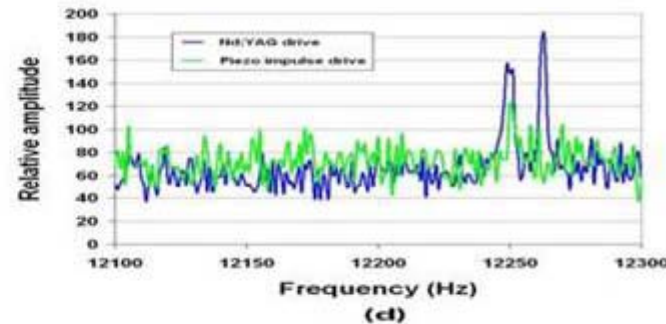
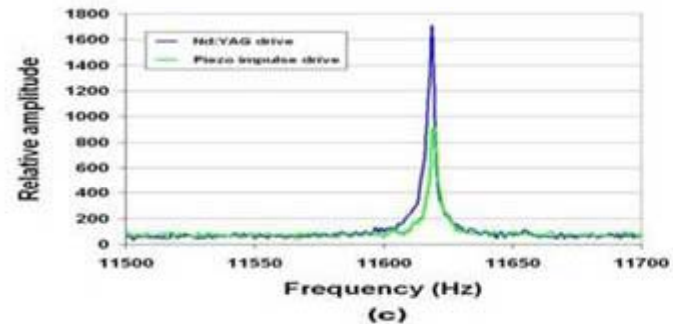
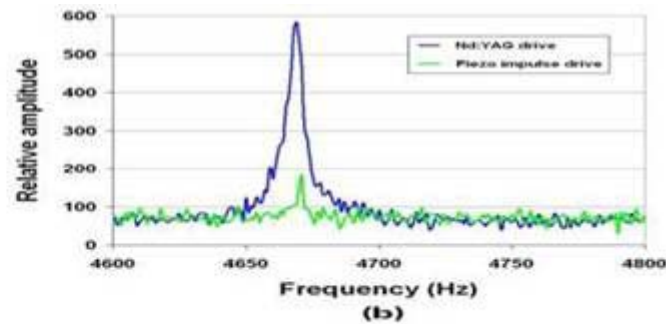
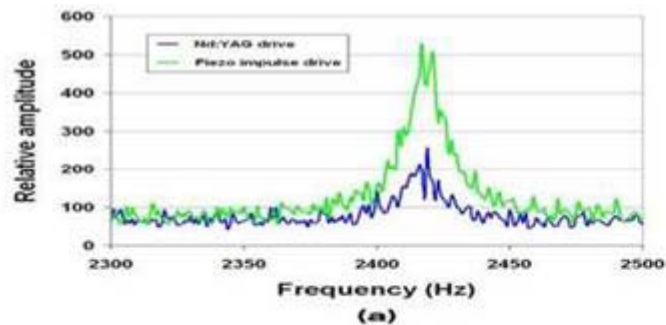


# Electrostatic activation



# Optical actuation

- 20 Hz Nd:YAG laser
  - Focusing causes ablation
  - Collimated beam
  - Impulse response



# Thermal expansion ?

- Energy absorbed: 
$$E_{abs}(z, \delta z) = \left( E_{incident} \times \frac{l^2}{\pi r^2} \times (1-R) \right) e^{-\frac{4\pi\kappa z}{\lambda}} \left( 1 - e^{-\frac{4\pi\kappa \delta z}{\lambda}} \right)$$

- Temperature increase: 
$$\Delta T(z, \delta z) = \frac{E_{abs}(z, \delta z)}{l^2 \delta z \rho c}$$

- Expansion: 
$$\Delta l(z, \delta z) = l \alpha \Delta T(z, \delta z)$$

$$E_{incident} \approx 1mJ$$

$$R = 37\%$$

$$r = 3mm$$

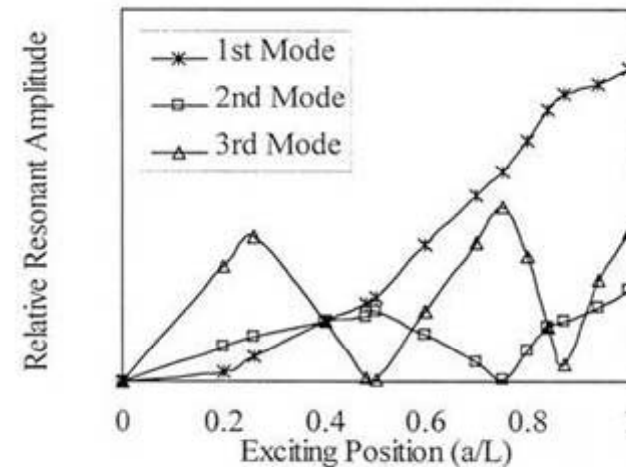
$$\alpha = 2.6 \times 10^{-6} K^{-1}$$

Depth $\delta z$ ( $\mu m$ )	Temperature increase (K)	Expansion (nm)
0 $\rightarrow$ 1.5	6.1	4.8
1.5 $\rightarrow$ 3	2.1	1.7

- To relieve stress, accelerometer must flex – vertical displacement  $\sim 80nm$ .

# Which mechanism ?

- Measurements comparable with piezo displacement of  $\sim 100\text{nm}$ .
- $\rightarrow$  thermal mechanism
- **However**, Yu et al tried point heat excitation
- $\rightarrow$  photon momentum



The resonant amplitude as a function of the exciting position. In the figure, the exciting position  $a$  represents the distance from the hinge.

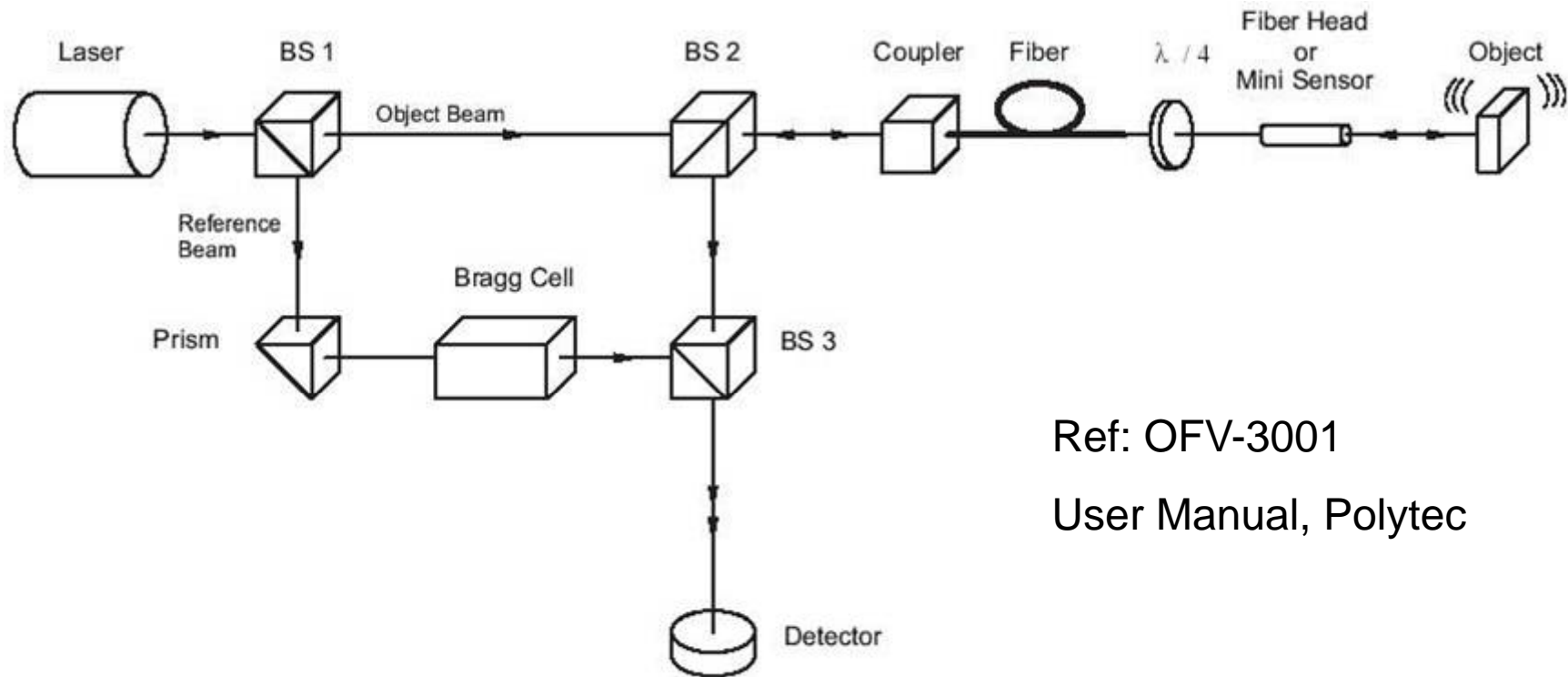
*Sensors and Actuators*, 77, 187-190, (1999)

# Polytec laser vibrometer

- Specifications:
  - wavelength 632 nm
  - frequency range:
    - 1.5 MHz (velocity)
    - 20 MHz (displacement)
  - picometer resolution
  - 20 mm working distance
- Rapid determination of natural frequency and damping
- Determination of modeshape (time consuming)



# Schematic of operation



Ref: OFV-3001

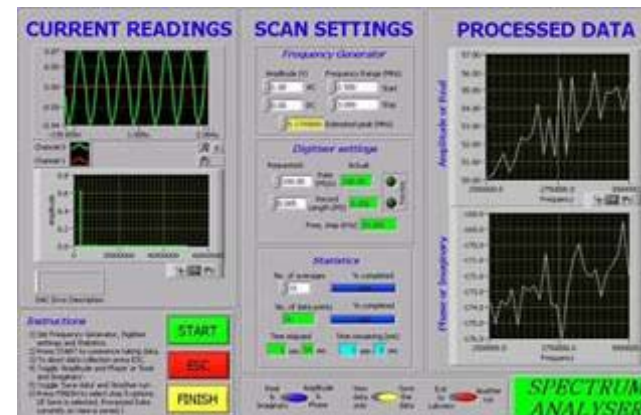
User Manual, Polytec

# Analysis

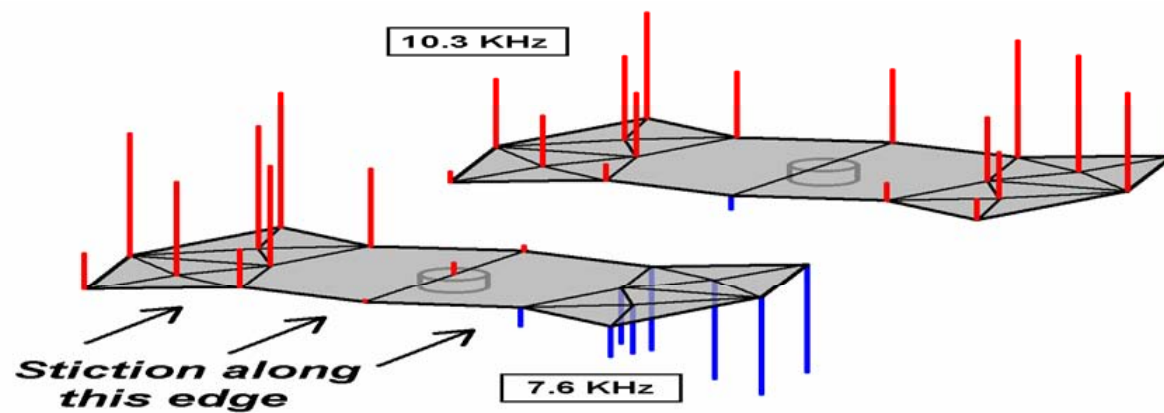
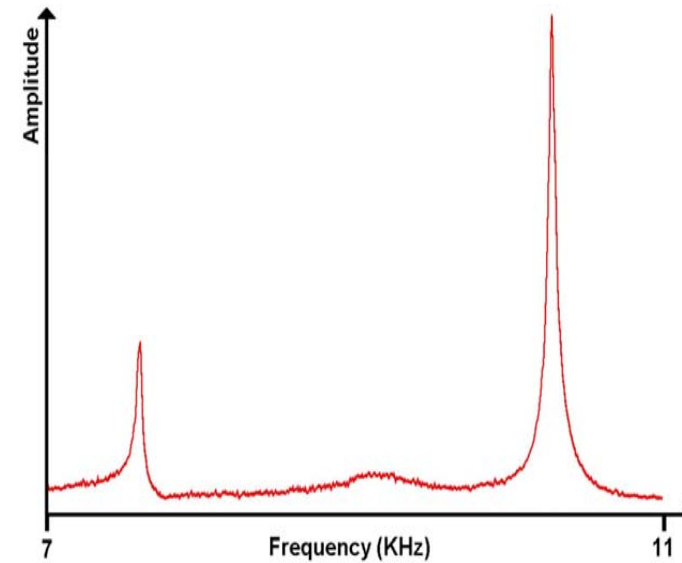
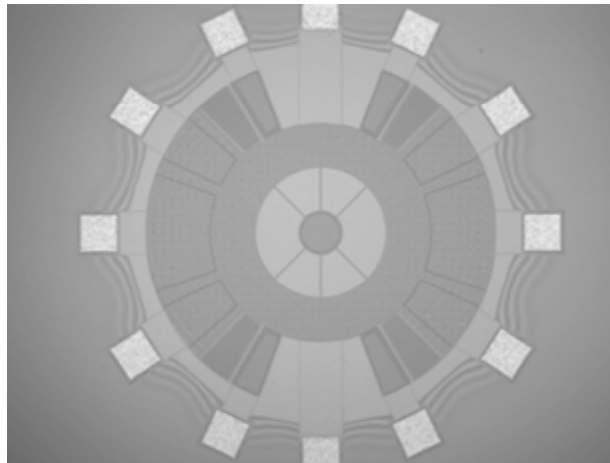
- 100 KHz analyser
  - 2 channel 21 bit
- 100 MHz (2.5 GHz)
  - 2 channel 8 bit



- Random noise
- Swept sine
- Impulse



# Typical measurement

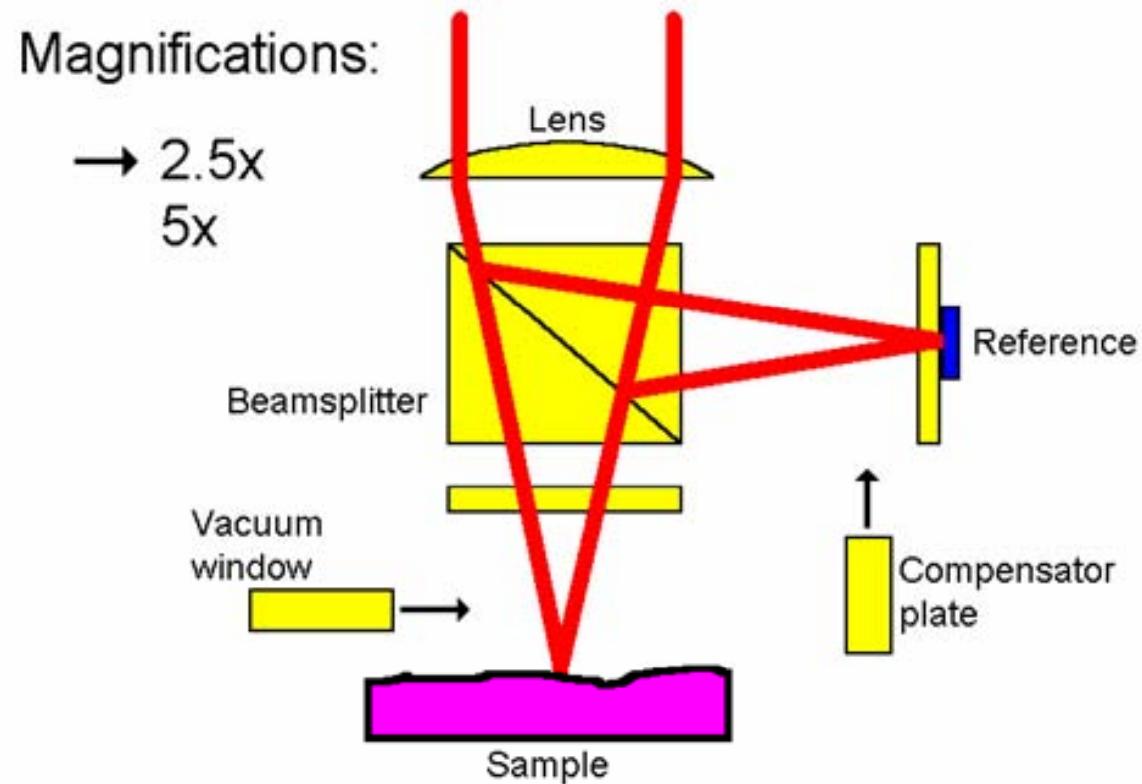


# Zygo NewView surface profiler

- Specifications:
  - 2.5X Michelson to 50X Mirau objectives
  - 20X adapted Linnik objective
  - 5.6 x 4.2 mm field of view (larger areas by stitching)
  - 640 x 480 data points
  - 0.1 nm resolution (over 5 mm)
  - 2.4  $\mu\text{m}/\text{s}$  scan speed
  - 10 mm working distance

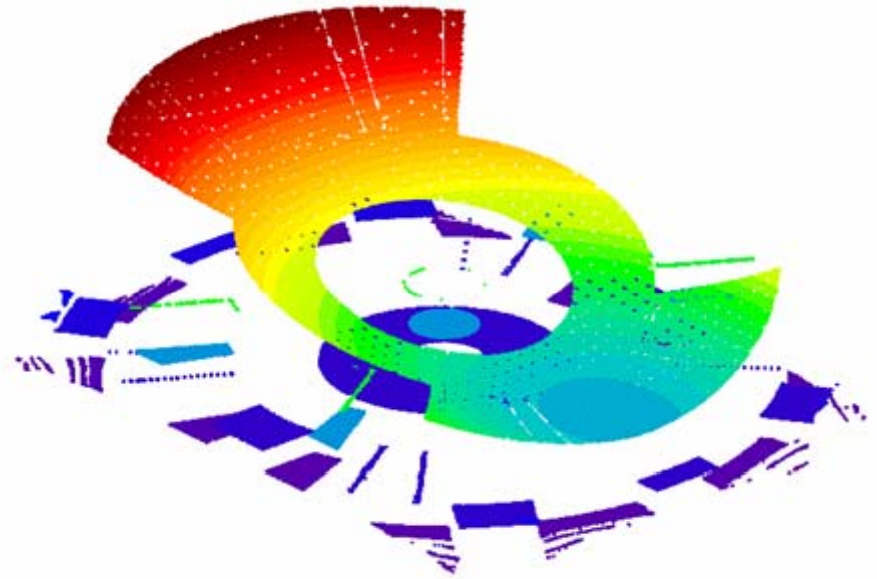
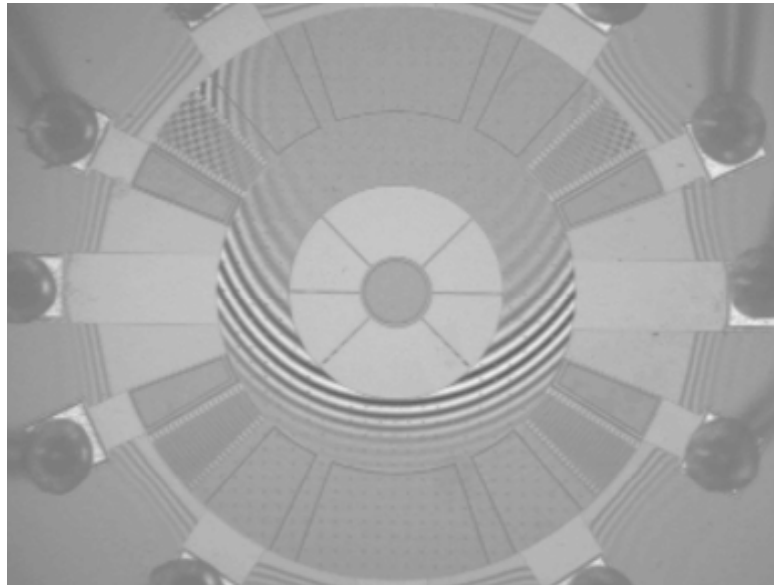


# Schematic of operation

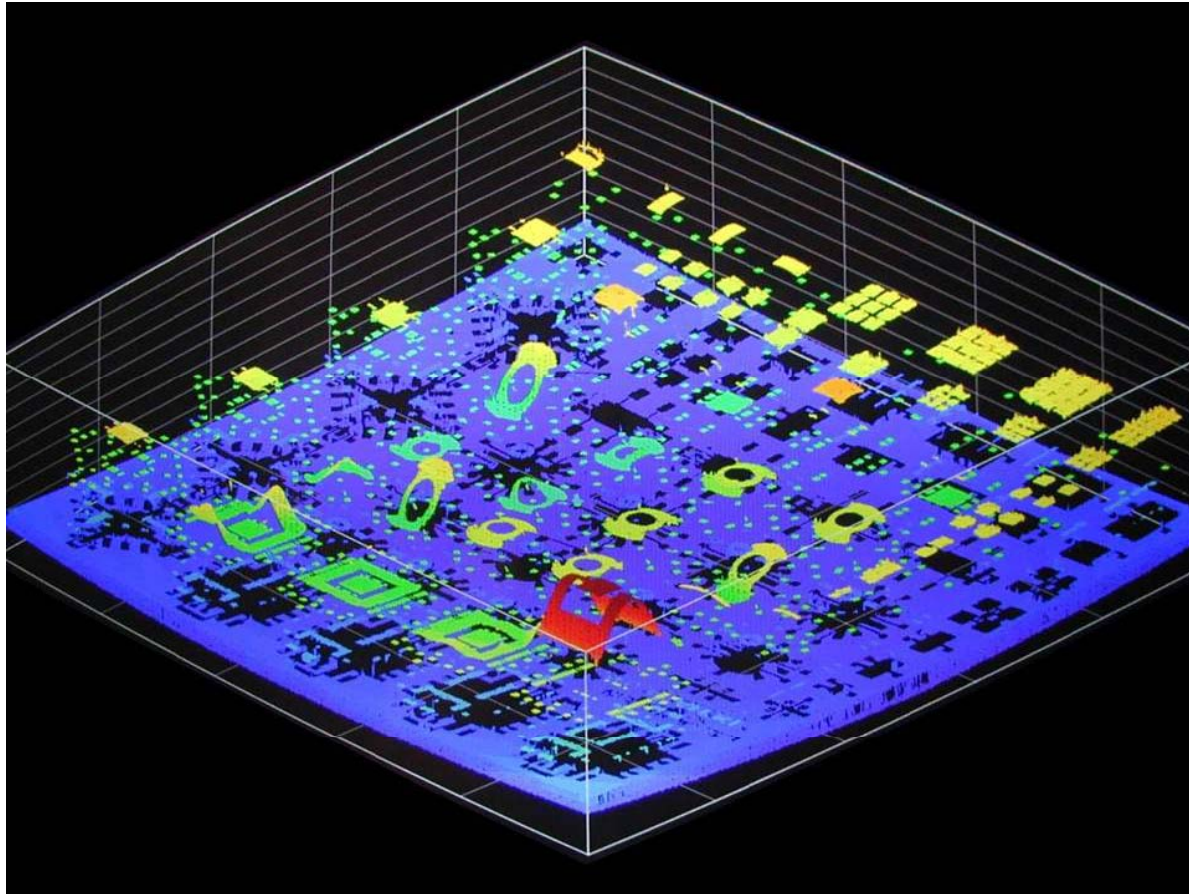


# Typical static measurement

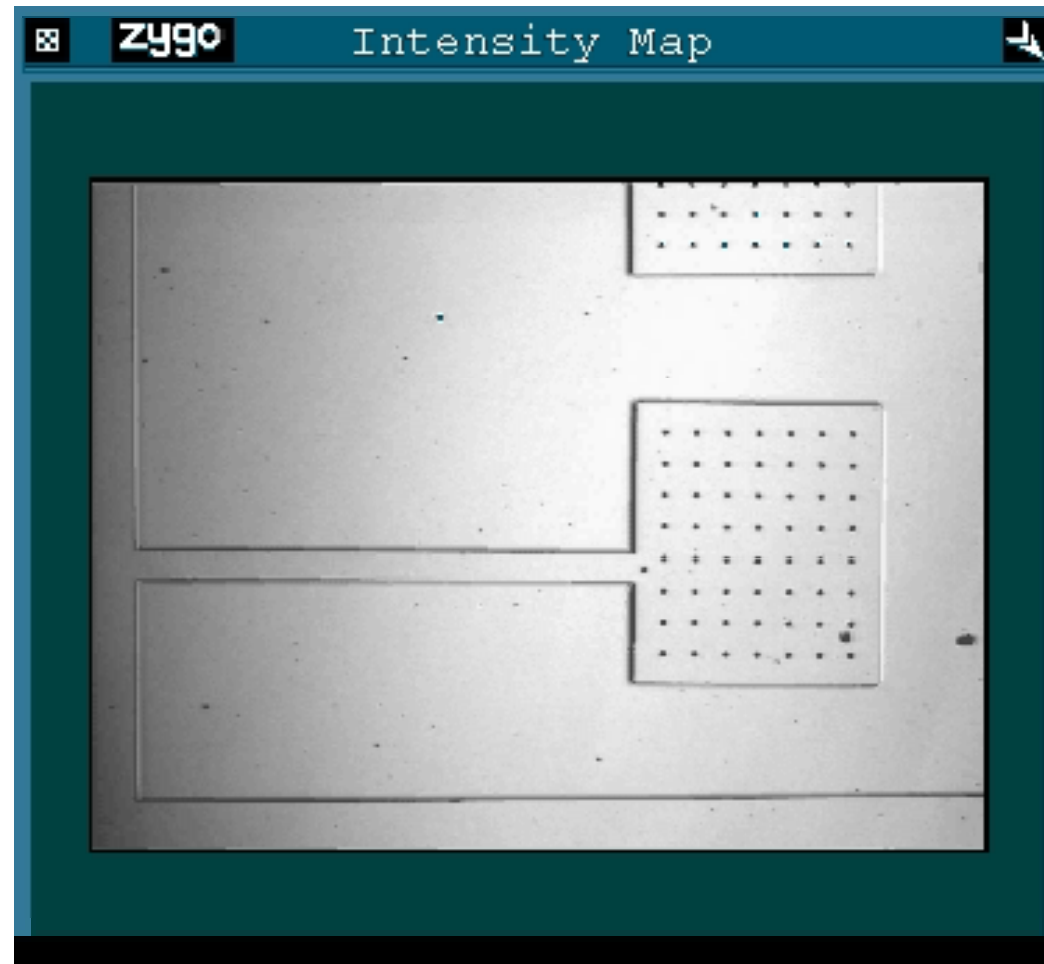
*QinetiQ bowtie gyroscope.*



# Typical static measurement

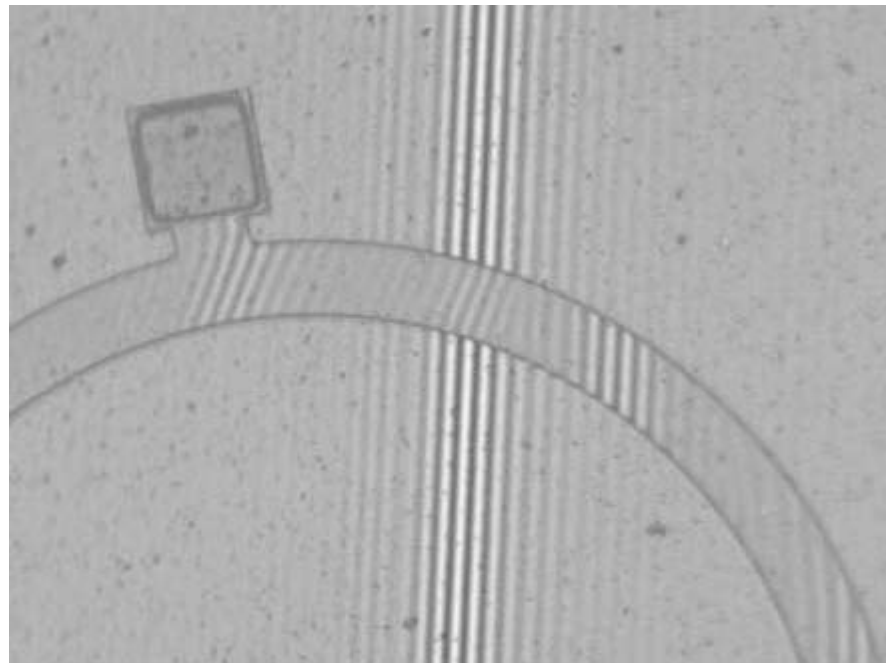


# Typical dynamic measurement

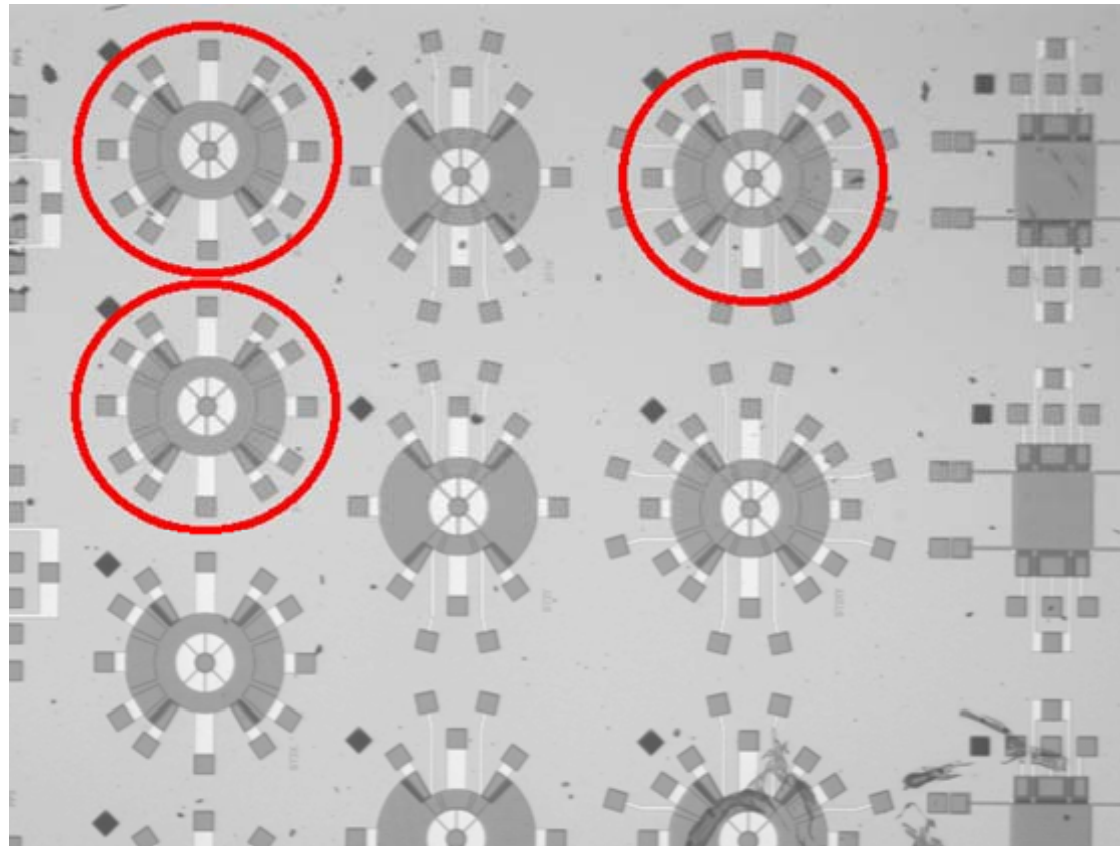


# Problems

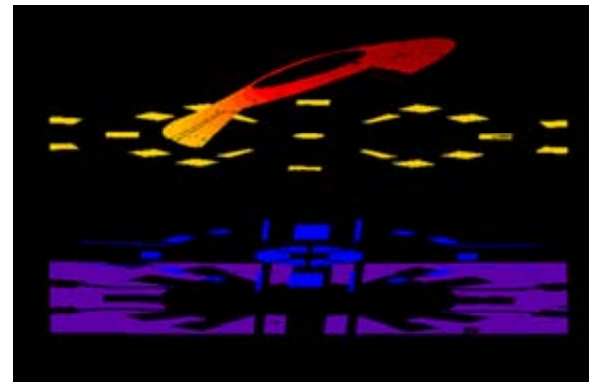
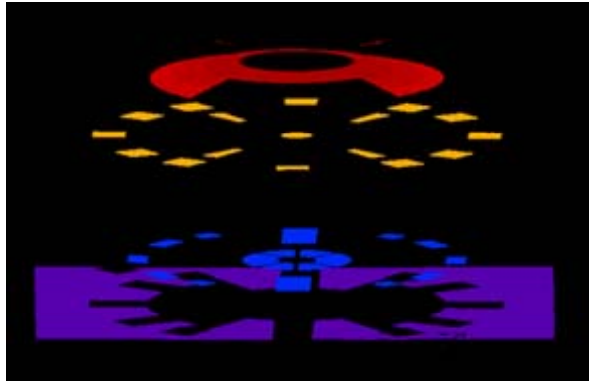
- Transparent layers
  - Appears as holes rather than hills
  - Multiple fringe sets



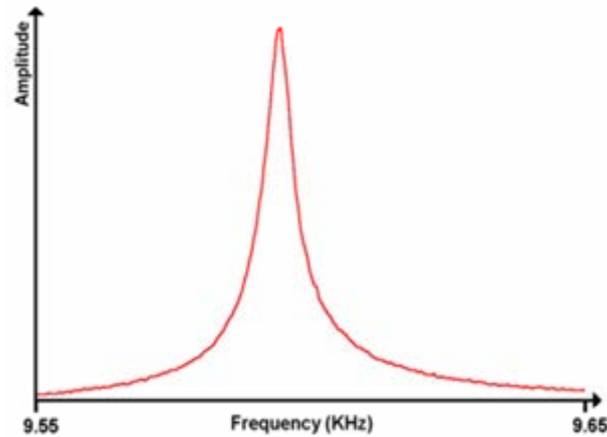
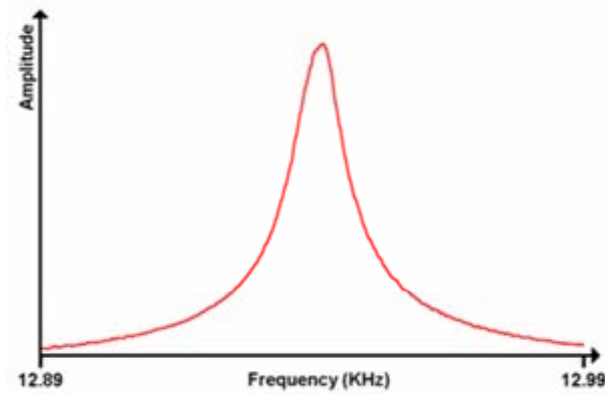
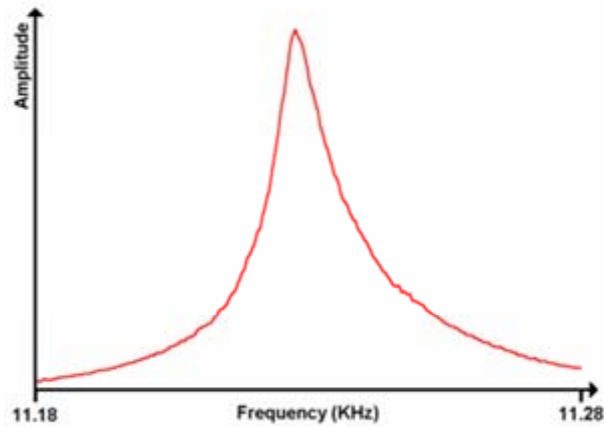
# Alternative dynamic measurement



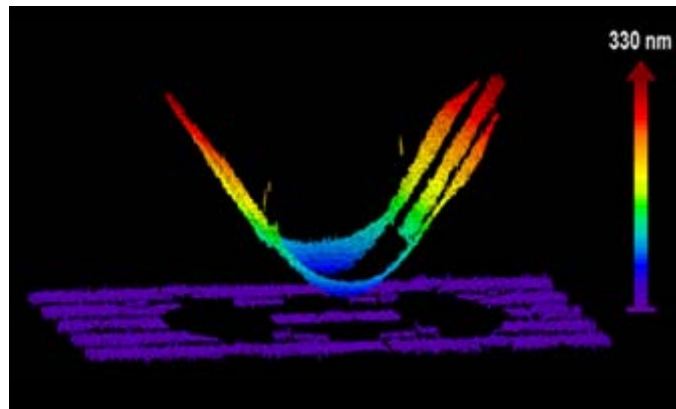
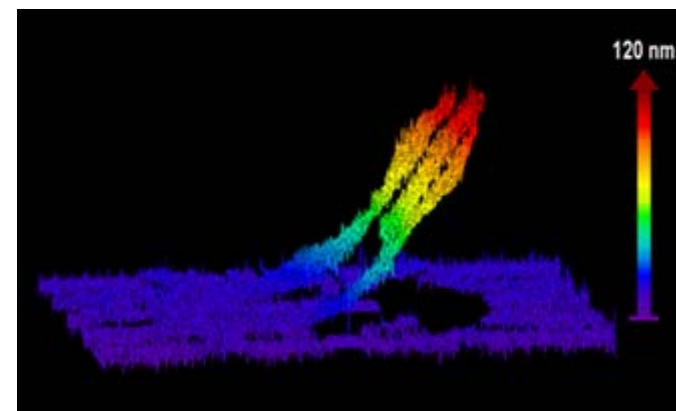
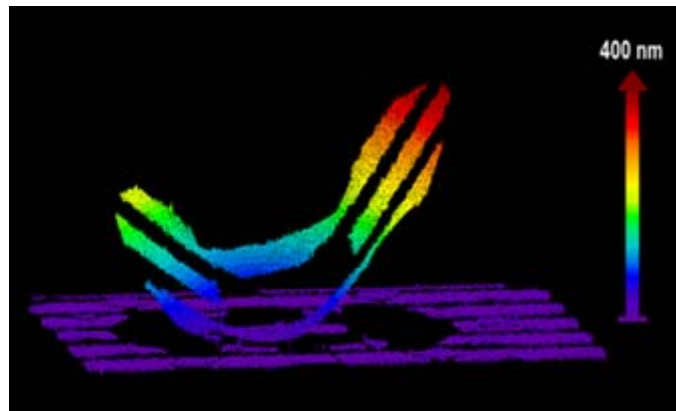
# Step 1: Profile



# Vibrometer measurement

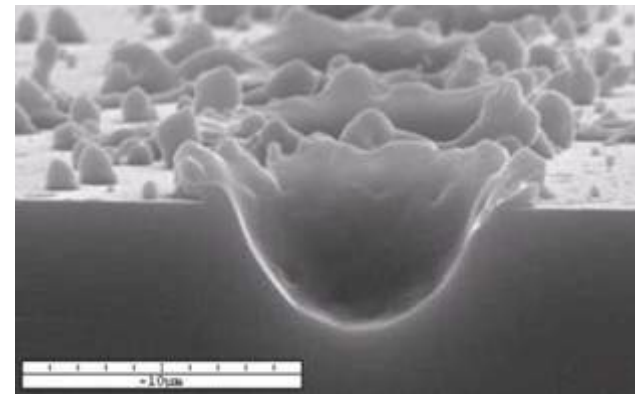


## Step 2: Apply $V$ and find difference

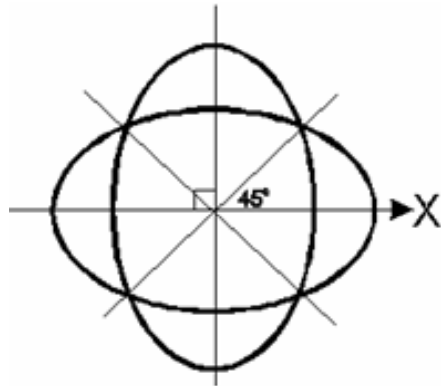


# MEMS modification

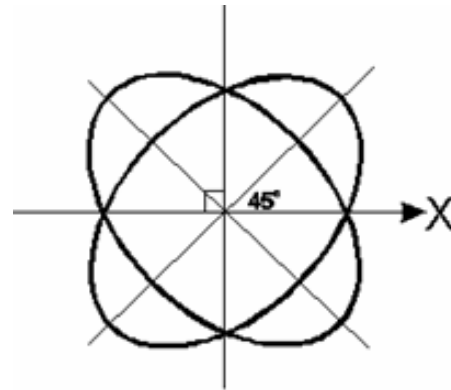
- Characteristics:
  - Wavelength 532 nm
  - Energy <160 mJ
  - Pulse width 4 ns (20 Hz)
- Debris is problematic



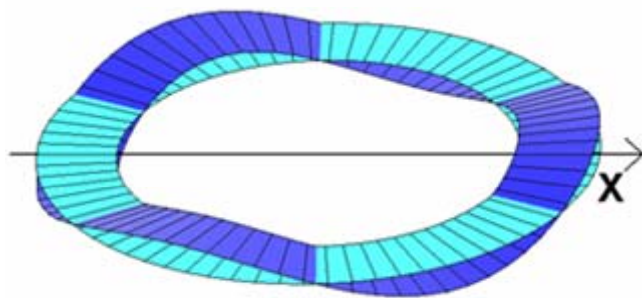
# Ex. 1: 3-axis gyroscope (B. Gallacher)



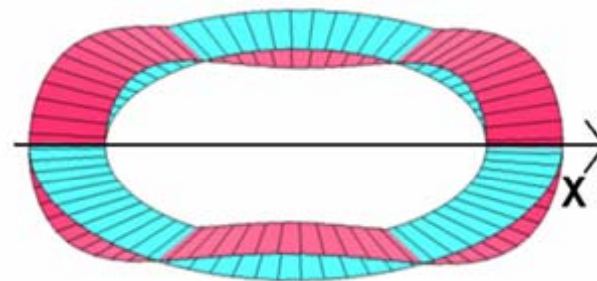
$\cos 2\phi$ :driven



$\sin 2\phi$ : $\Omega_z$

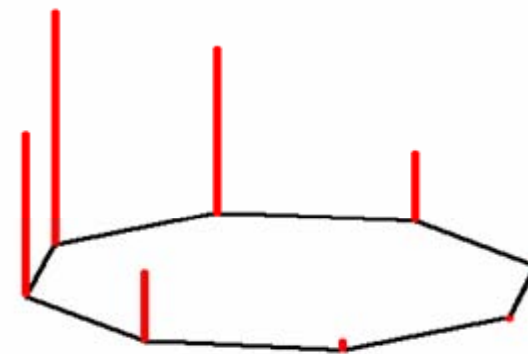
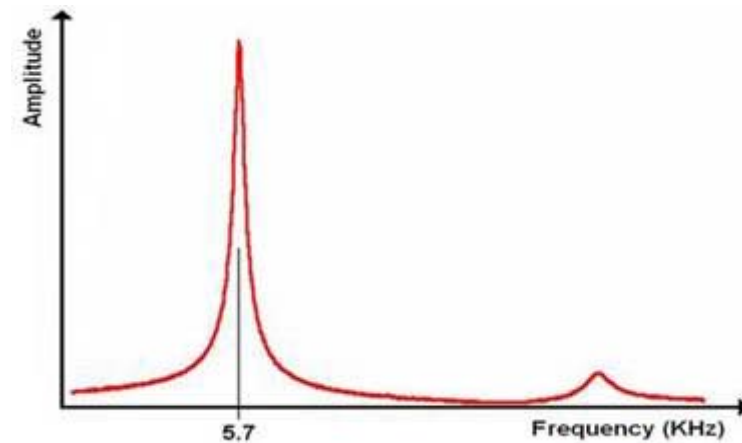
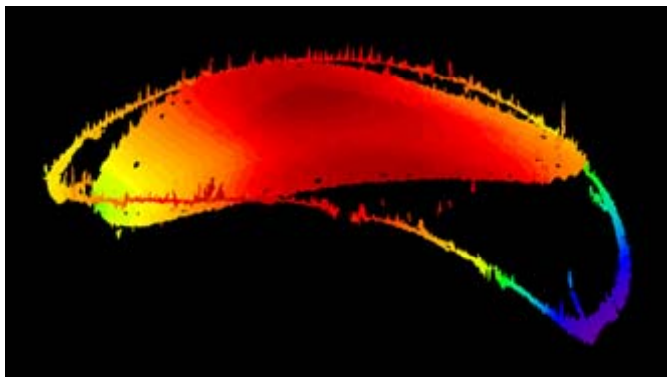
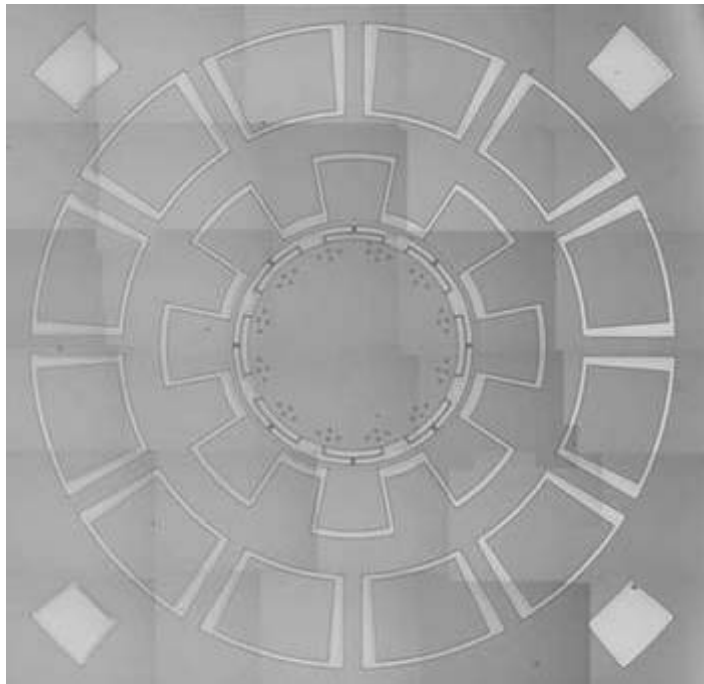


$\cos 3\phi$ : $\Omega_y$

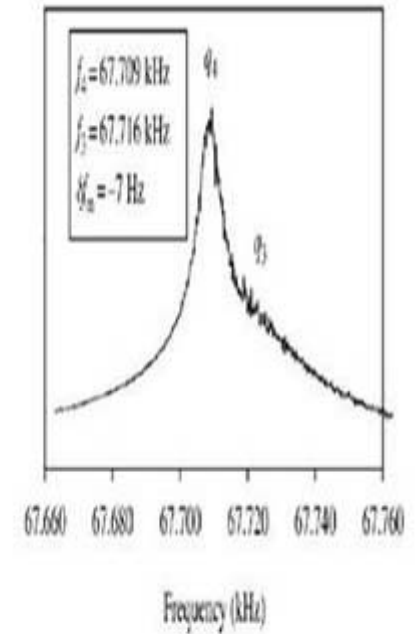
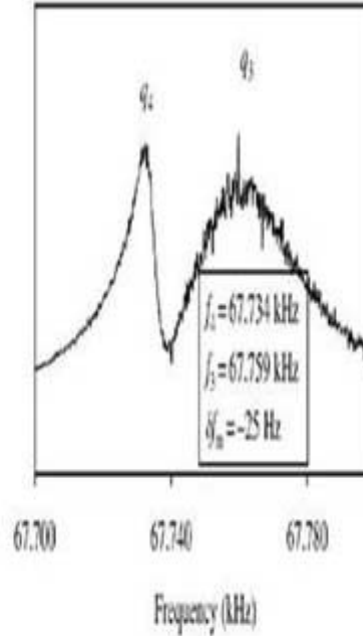
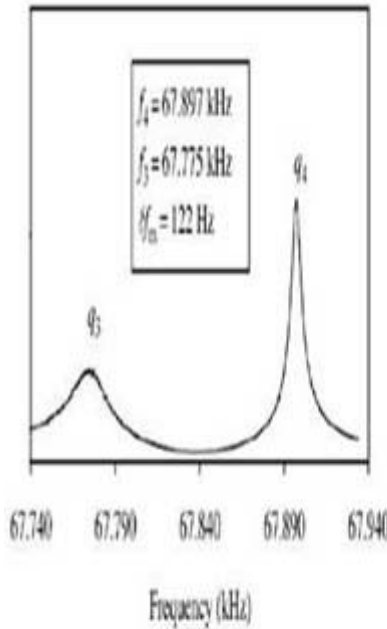
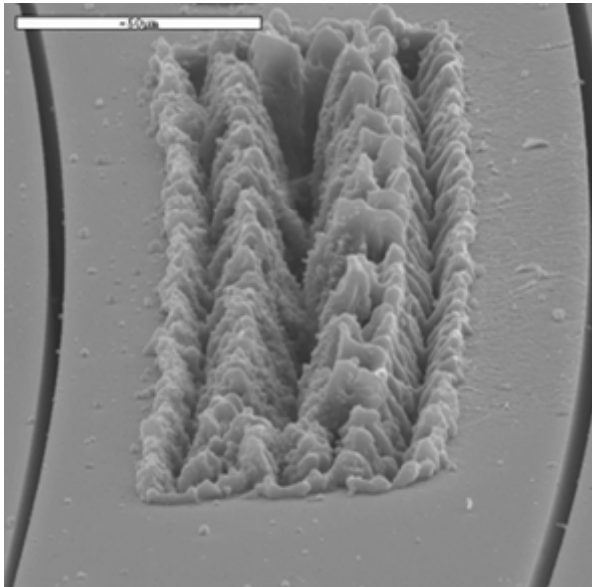


$\sin 3\phi$ : $\Omega_x$

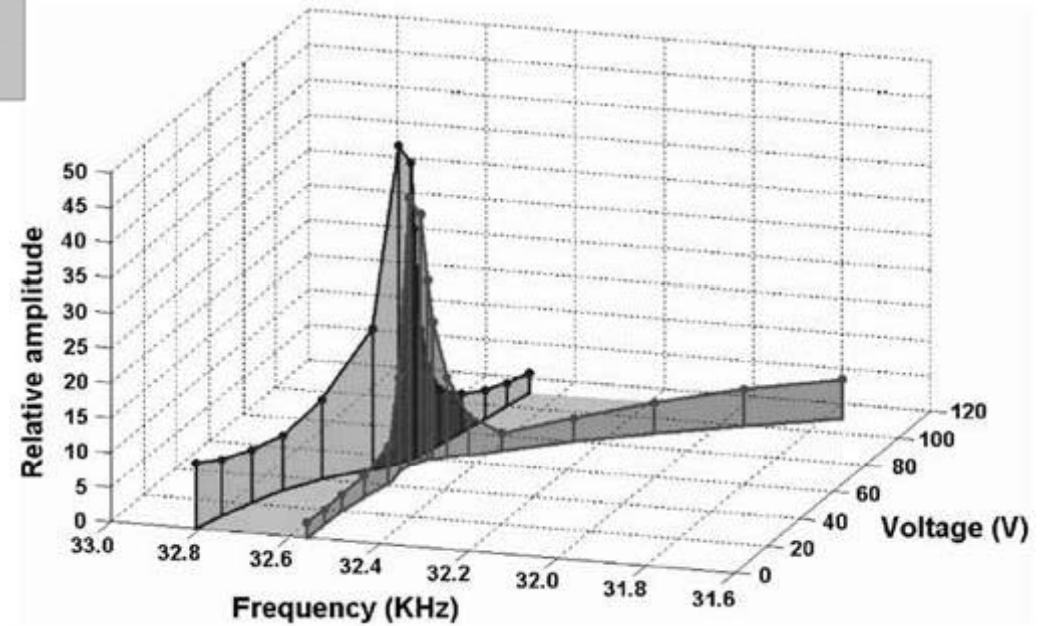
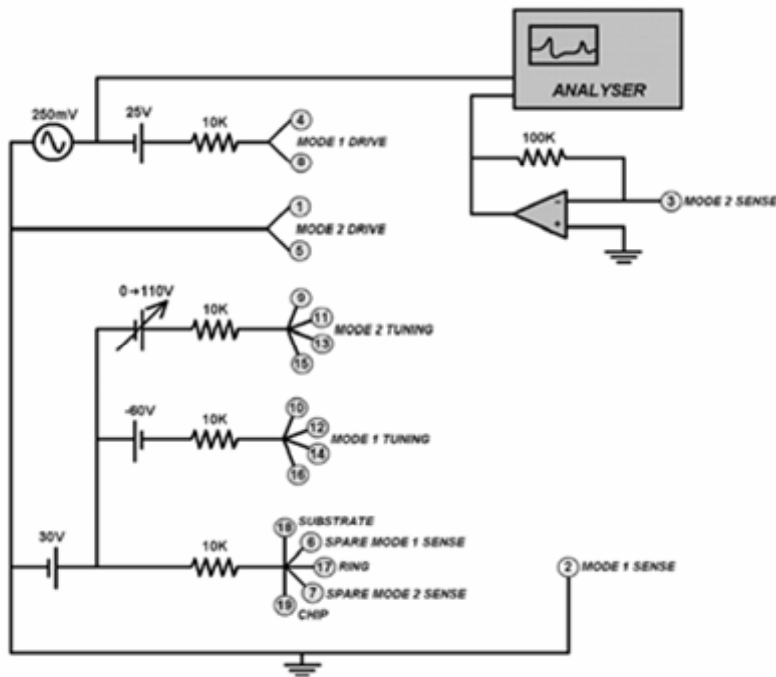
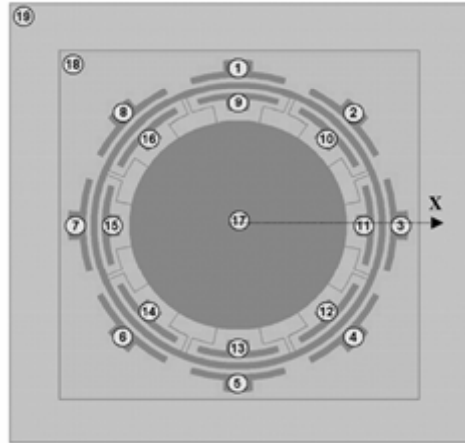
# Ex. 1: 3-axis gyroscope (B. Gallacher)



# Passive mode tuning



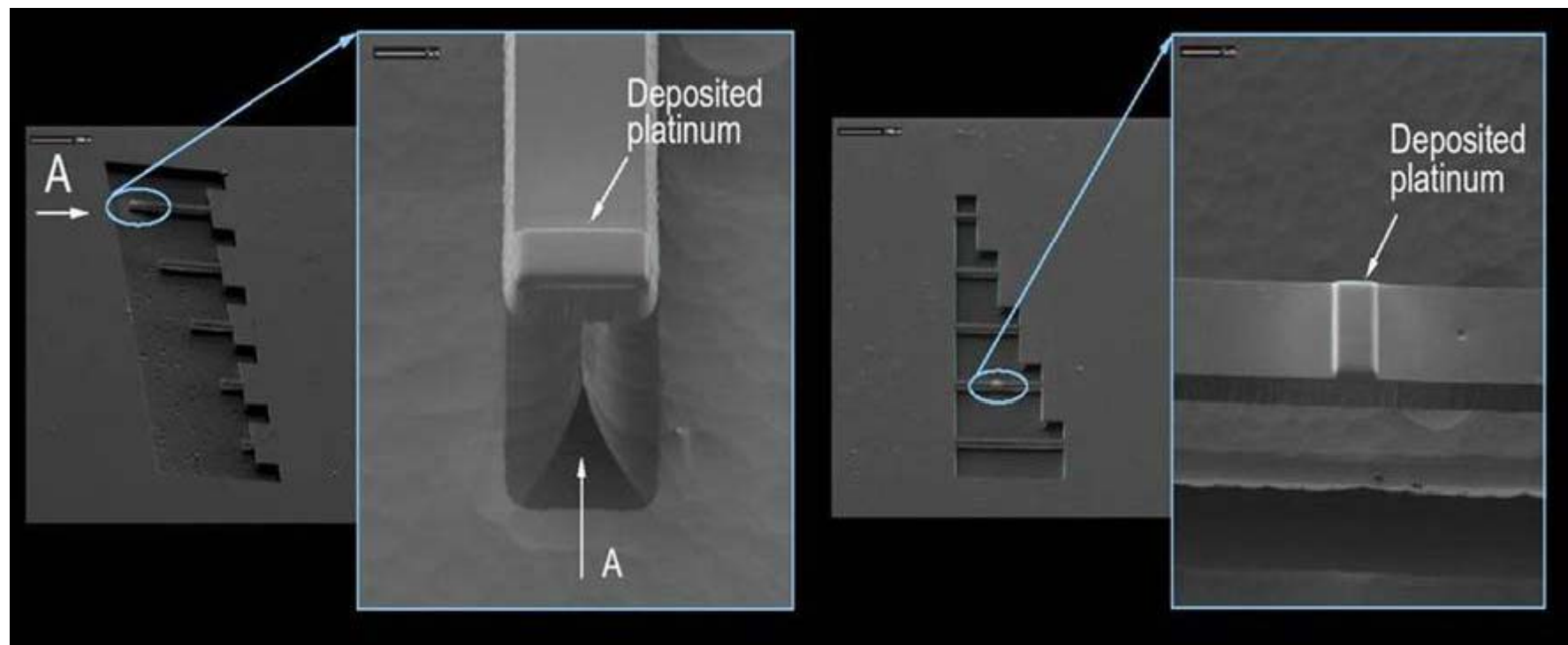
# Active tuning



# Digital signal processing

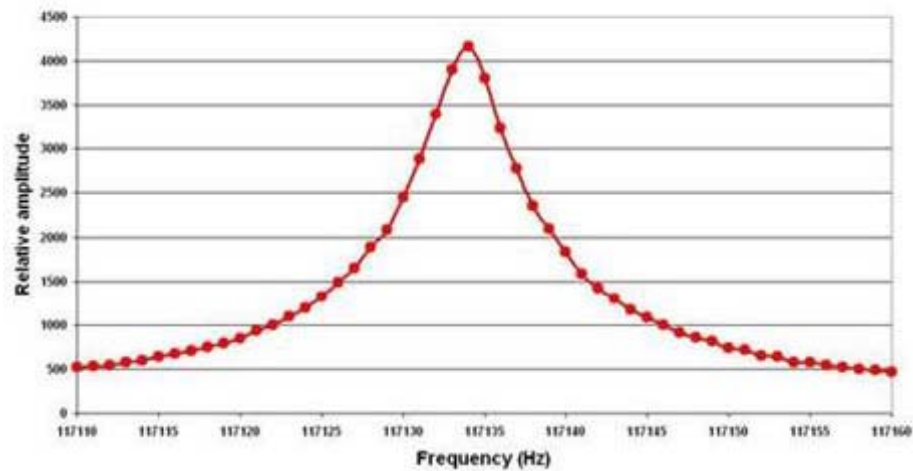


## Ex. 2: FIB tuning (R. Cheung, Edinburgh)

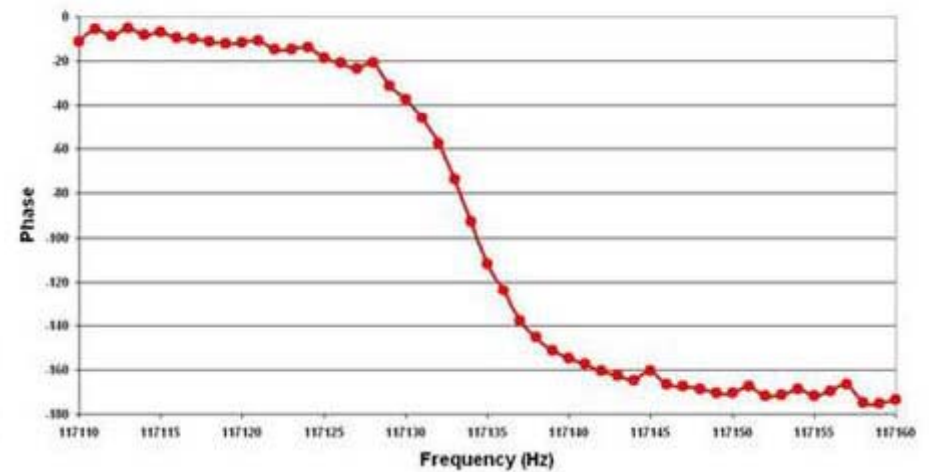


# Cantilever frequency determination

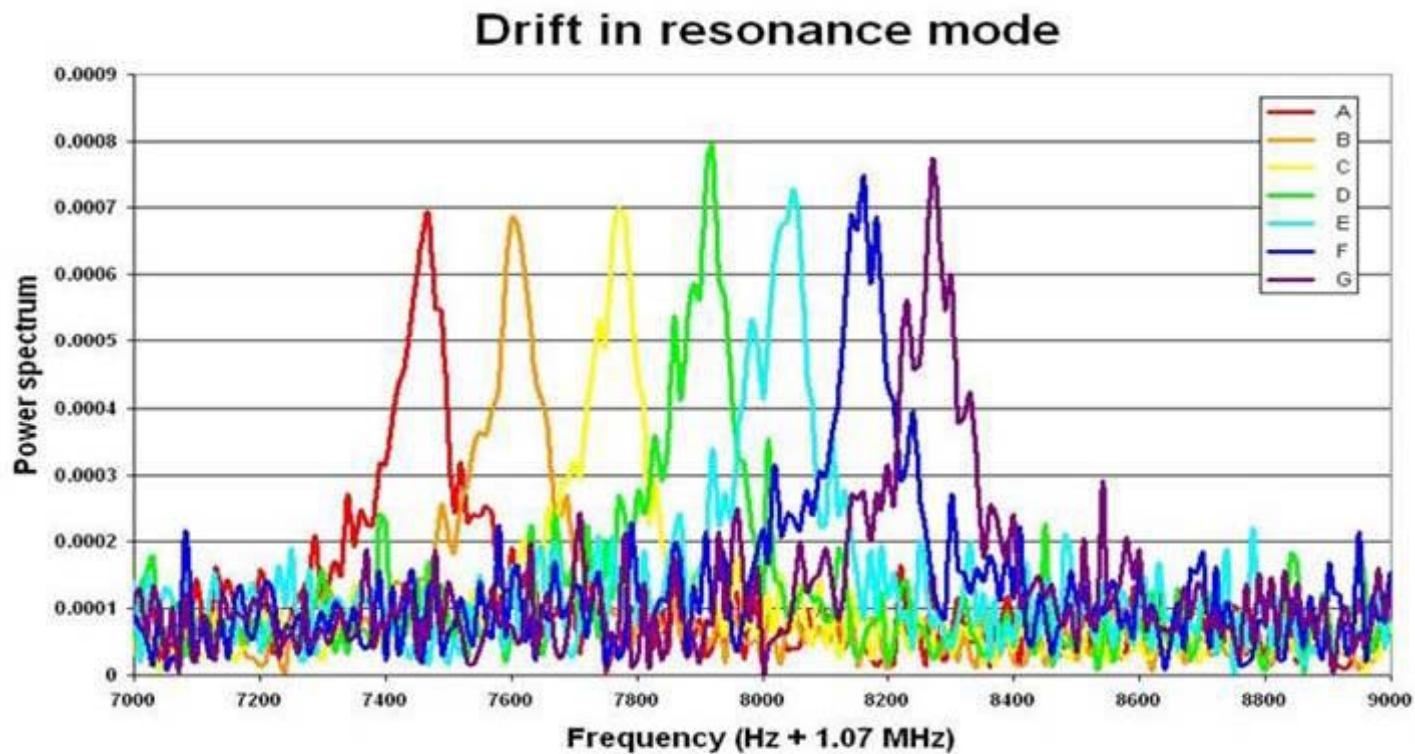
Cantilever resonance frequency



Cantilever resonance frequency



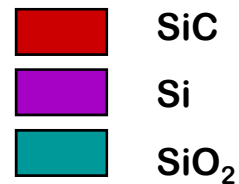
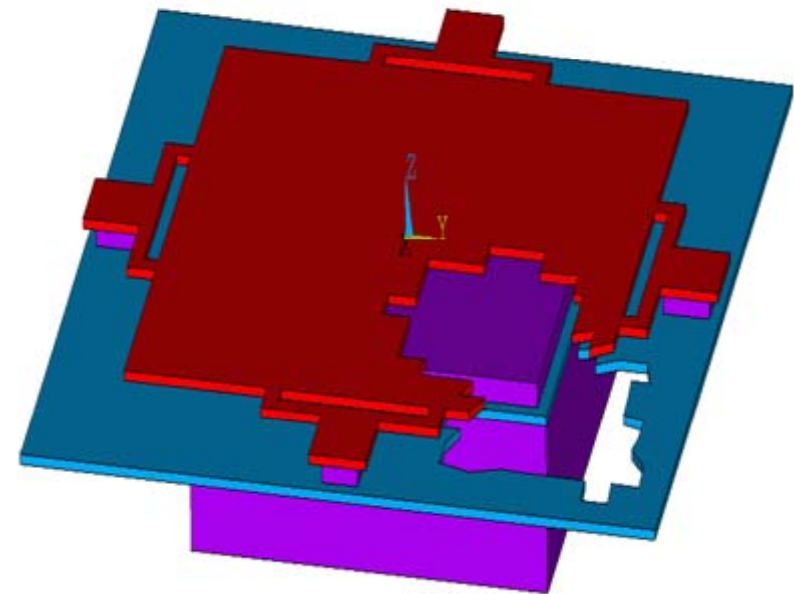
# Bridge frequency determination



- Heating causes a drift in resonance frequency

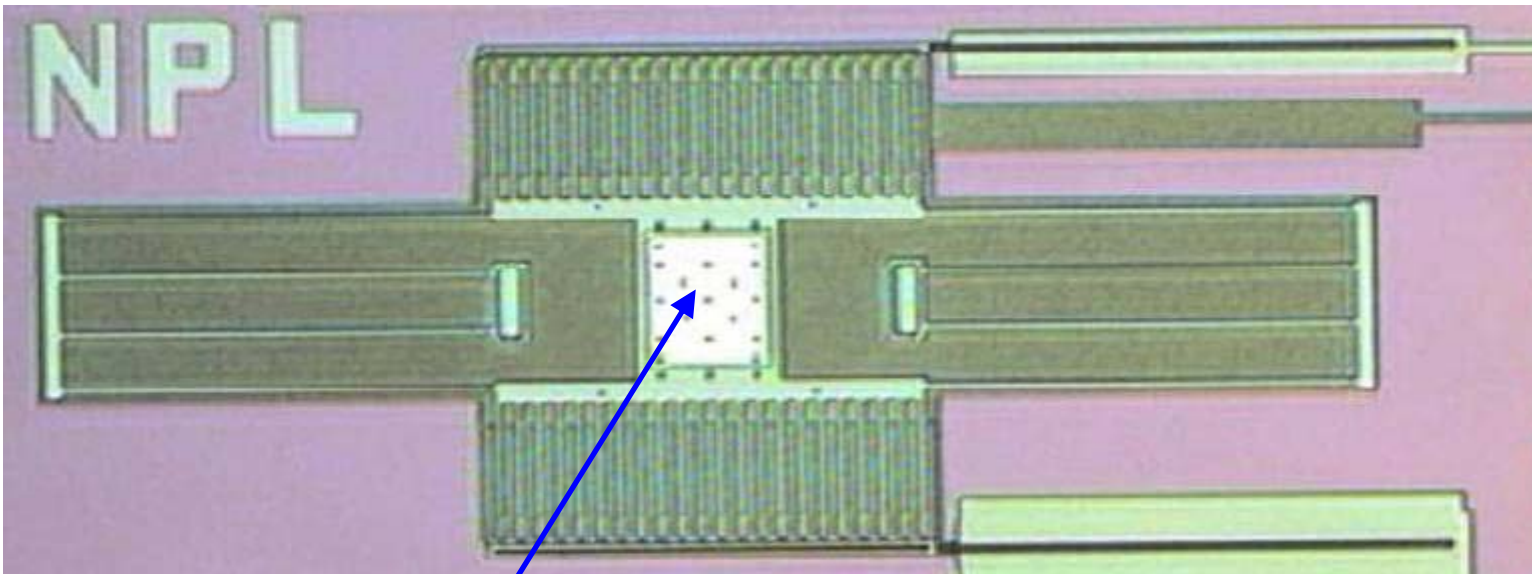
# High temperature MEMS

- High temperature SiC devices and electronics
- Custom vacuum chamber developed for 800°C measurements.



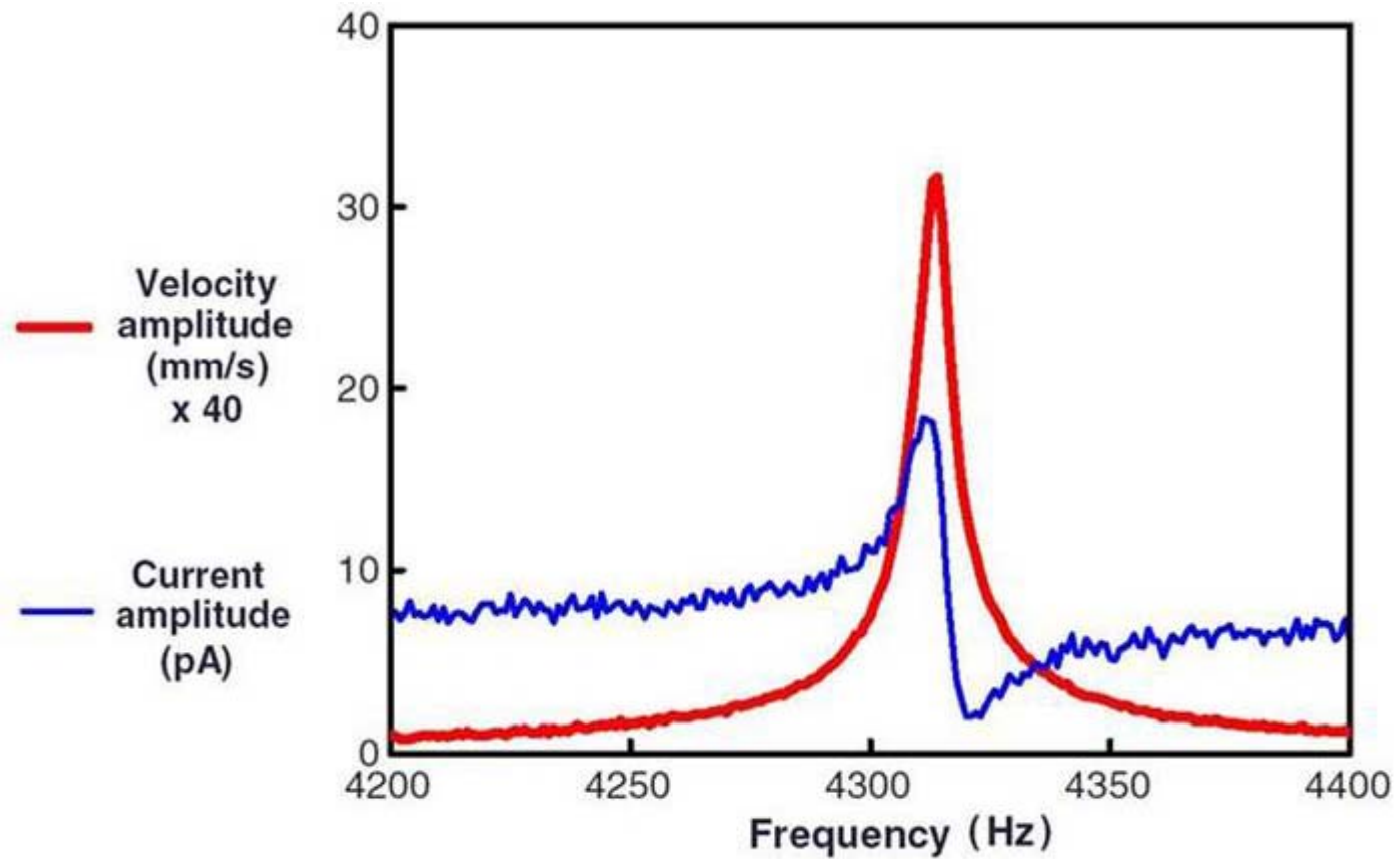
## Ex. 3: AFM calibration (P. Cumpson, NPL)

- MEM device for AFM calibration



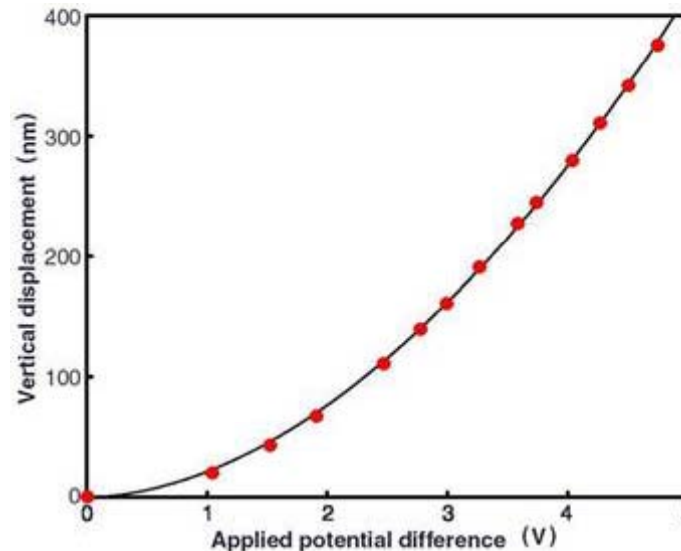
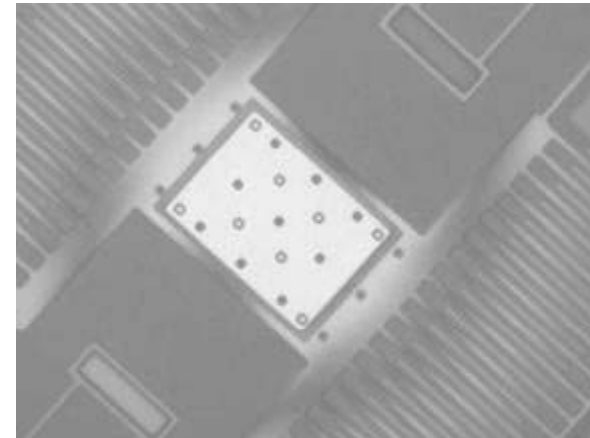
Gold pad to aid reflection.

# Dynamic characterization



# Static characterization

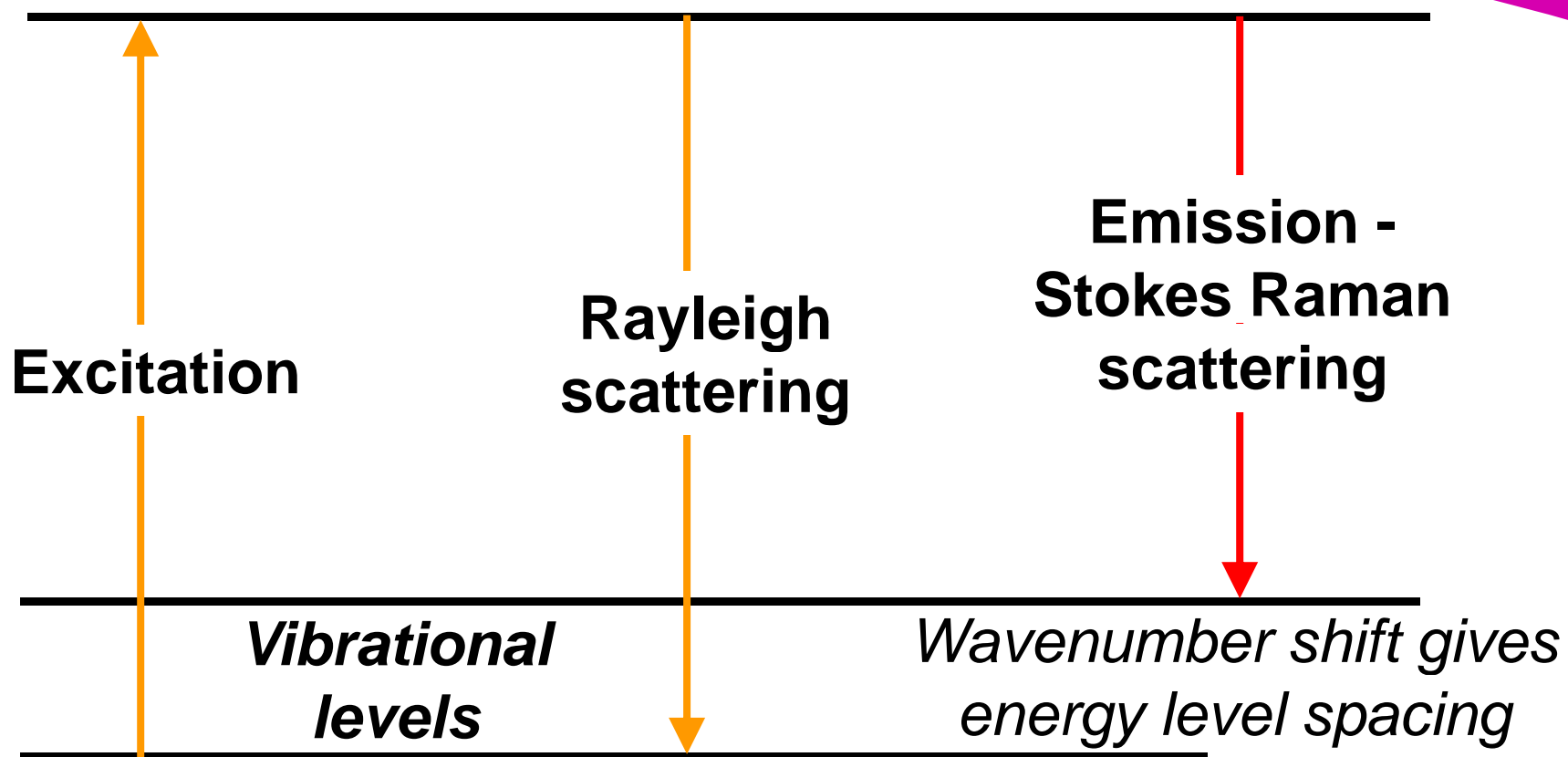
- Static deflections must be performed under vacuum.
- Compensated objective required (Linnik).
- Measured to 1nm resolution.



# Current capabilities

- Mounting and actuation options.
- Static measurements to  $1\mu\text{m} \times 1\mu\text{m} \times 1\text{nm}$ .
- Dynamic measurements to 20 MHz and  $\sim 10\text{ pm}$ .
- Measurement issues resolved 'in situ'.
  
- Problem - spatial and dynamic limitations make MEMS and NEMS characterization a continuing problem.
- Possible solution – Raman spectroscopy

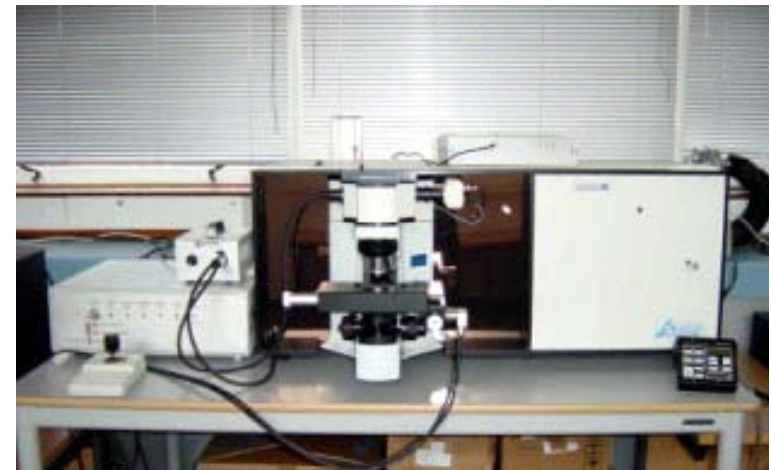
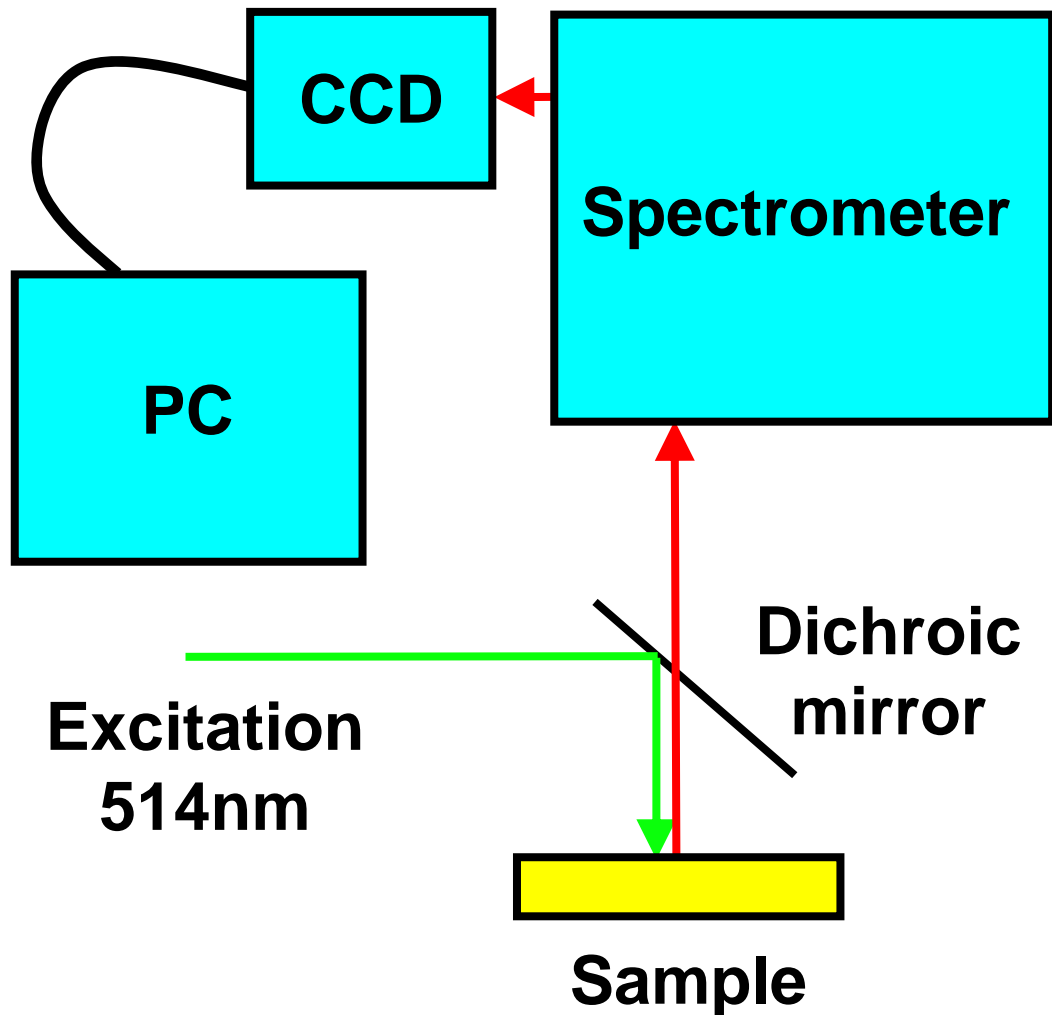
# Raman spectroscopy



# Measuring strain

- Silicon gives a (triple degenerate) Raman peak at  $520.8 \text{ cm}^{-1}$ , strain in the silicon shifts this peak (lower wavenumbers when in tension).
- Shift in the Raman peak was shown to correspond to the volumetric strain in the unit cell [Anastassakis et al].
- A four point bending experiment [Bowden et al] determined this shift to be  $5.2 \times 10^{-4} \text{ cm}^{-1}$  per volumetric  $\mu\text{strain}$  ( $TO_z$  phonon).
- For dynamic experiments, require either strobed measurement [Xue et al] or continuous (averaged) measurement.

# Raman equipment



# Experimental geometry

- Raman tensors,  $R_j$ , are [Loudon]:

$$TO_x = \begin{pmatrix} 0 & 0 & 0 \\ 0 & 0 & d \\ 0 & d & 0 \end{pmatrix}, TO_y = \begin{pmatrix} 0 & 0 & d \\ 0 & 0 & 0 \\ d & 0 & 0 \end{pmatrix}, LO_z = \begin{pmatrix} 0 & d & 0 \\ d & 0 & 0 \\ 0 & 0 & 0 \end{pmatrix}$$

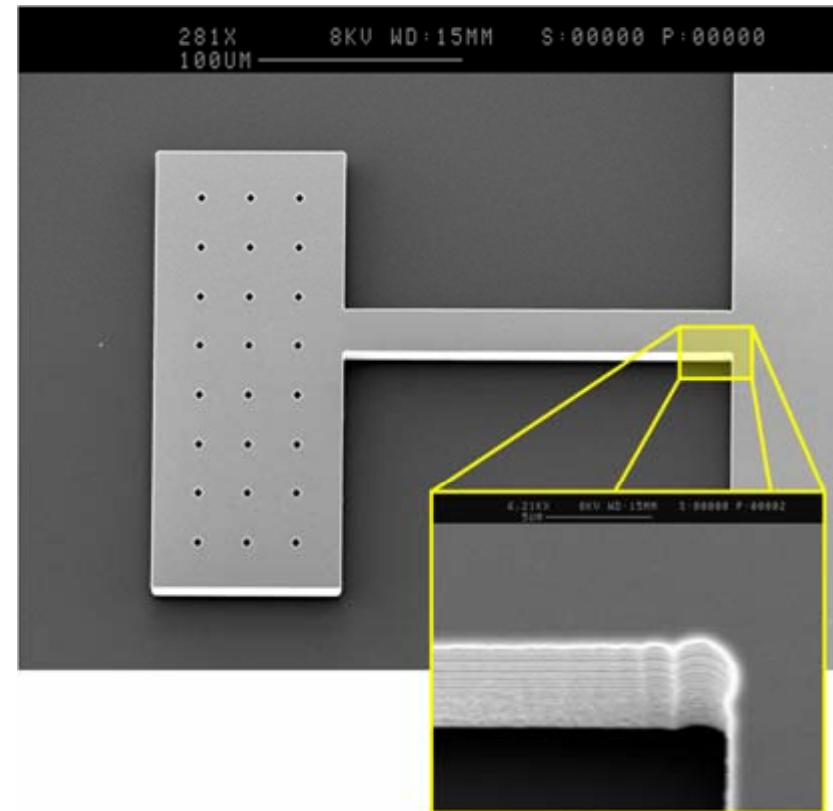
- For incident and scattered polarizations,  $p_i$  and  $p_s$ , Raman intensity given by:

$$I = |p_s R_j p_i|^2$$

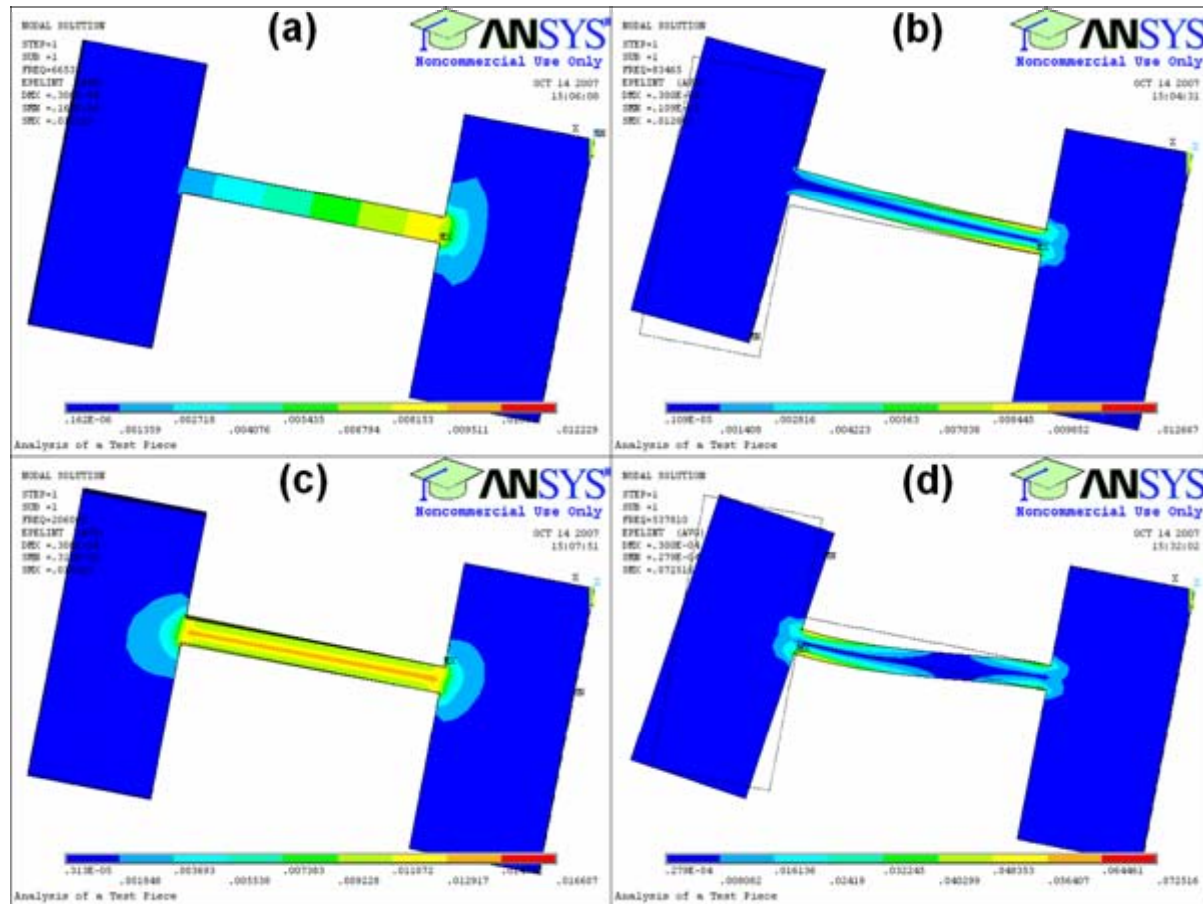
- For geometry here ( $\langle 100 \rangle$ ,  $0^\circ$  incident,  $180^\circ$  scattered), only  $TO_z$  photon observed.

# Test structures

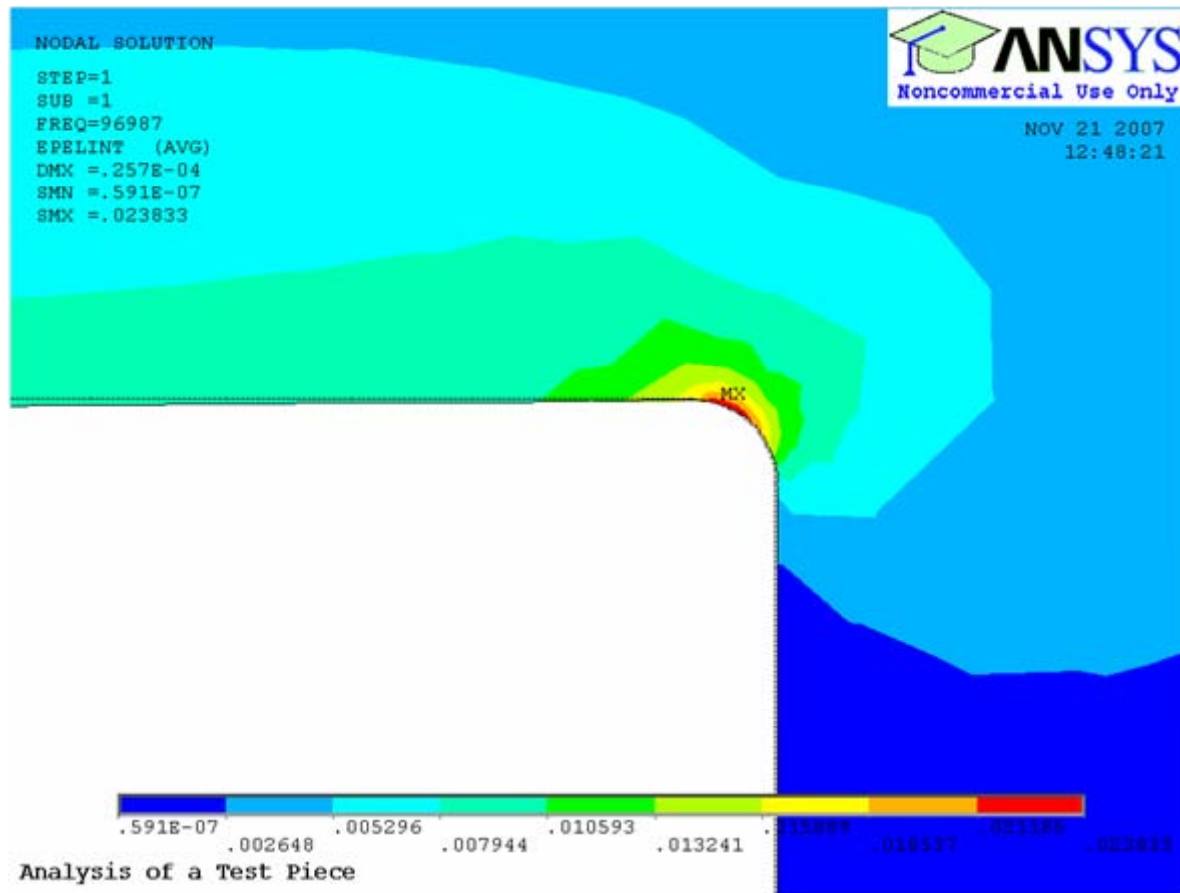
- Simple  $\langle 100 \rangle$  SOI test structures
- Beam section is  $200 \times 20 \times 16 \mu\text{m}$
- Easily actuated
  - in-plane
  - out-of-plane
  - twisting



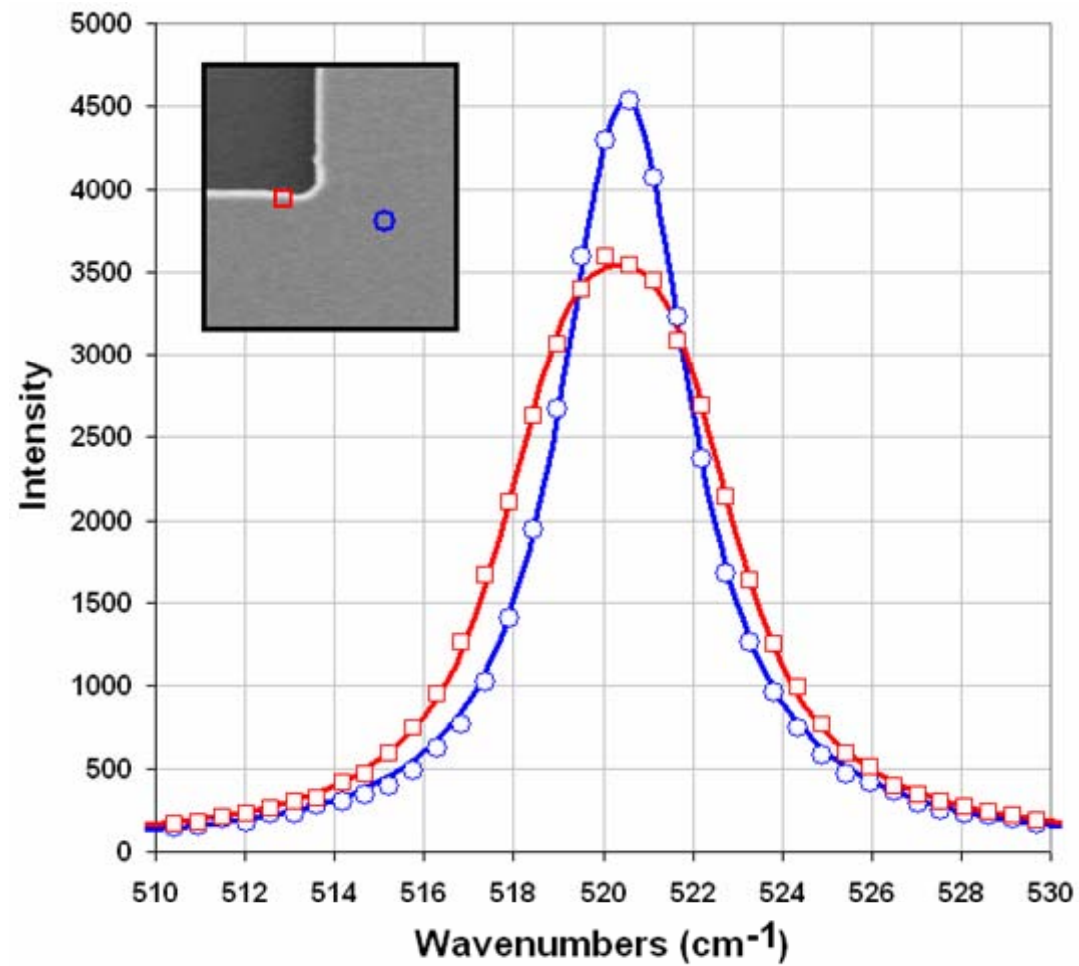
# Modelling - strain indicates mode shape



# Modelling of strain concentration



# Typical spectra

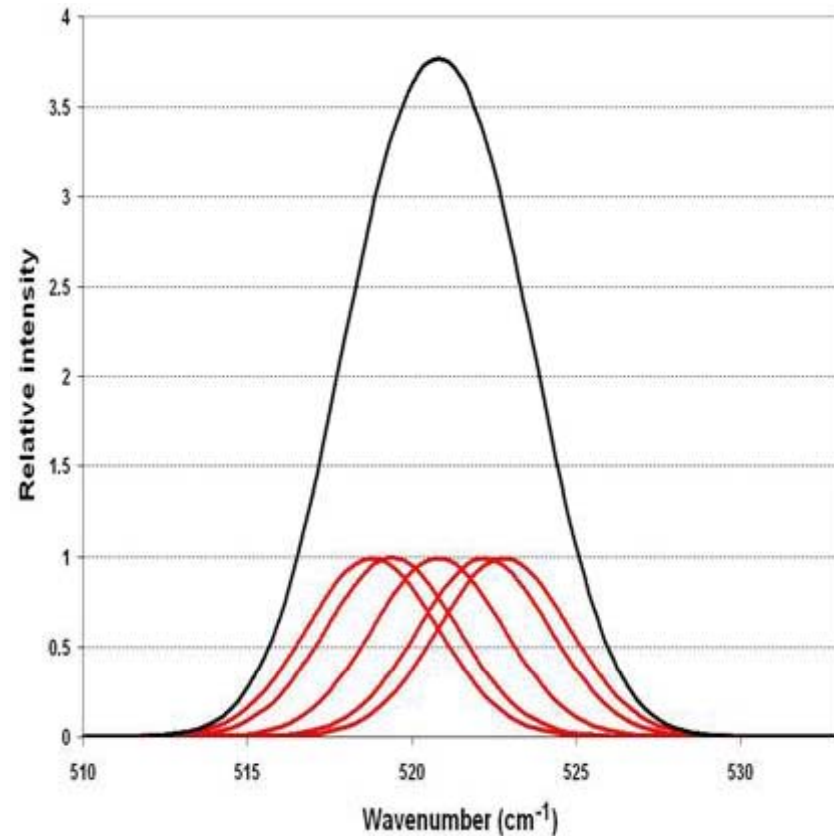


# Fitting the spectra

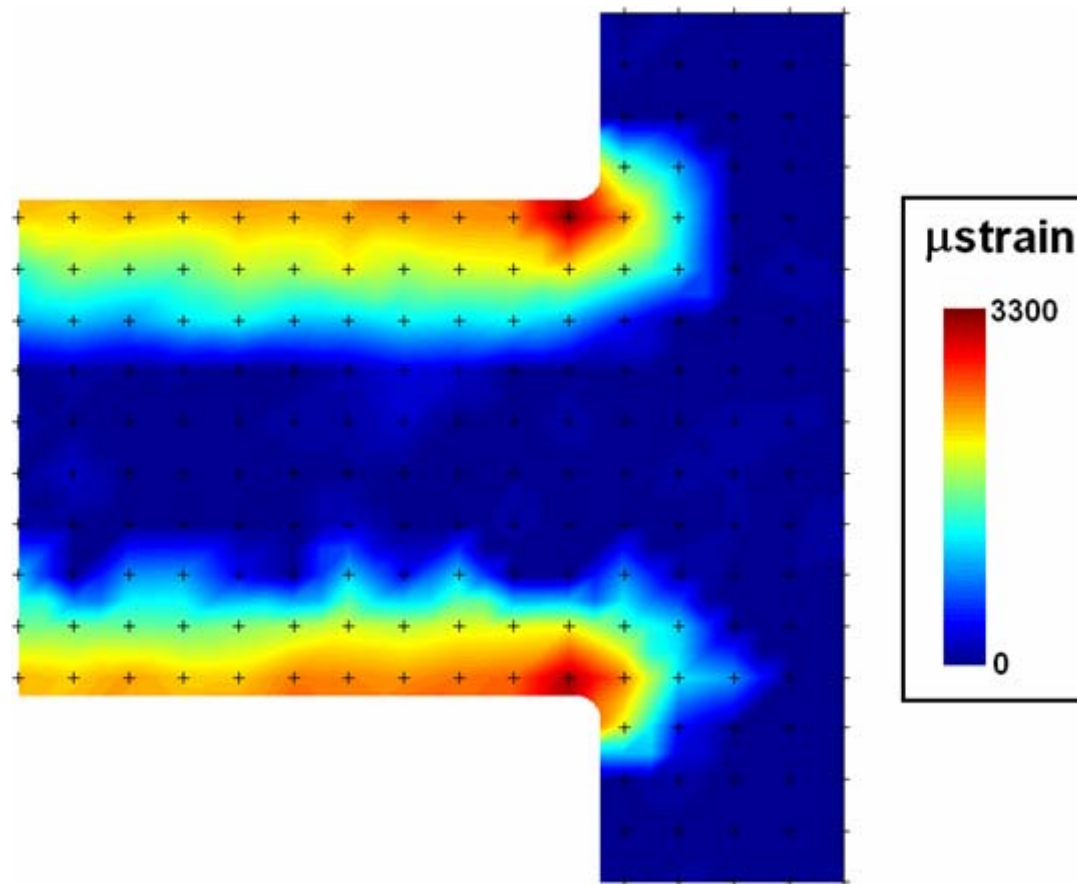
- Voigt profile determined from static measurement.
- Sum of a spread of Voigt profiles,  $V(\nu_0)$ , gives overall profile,  $P$ :

$$P = \sum_{\theta=0}^{2\pi} V(A \sin \theta)$$

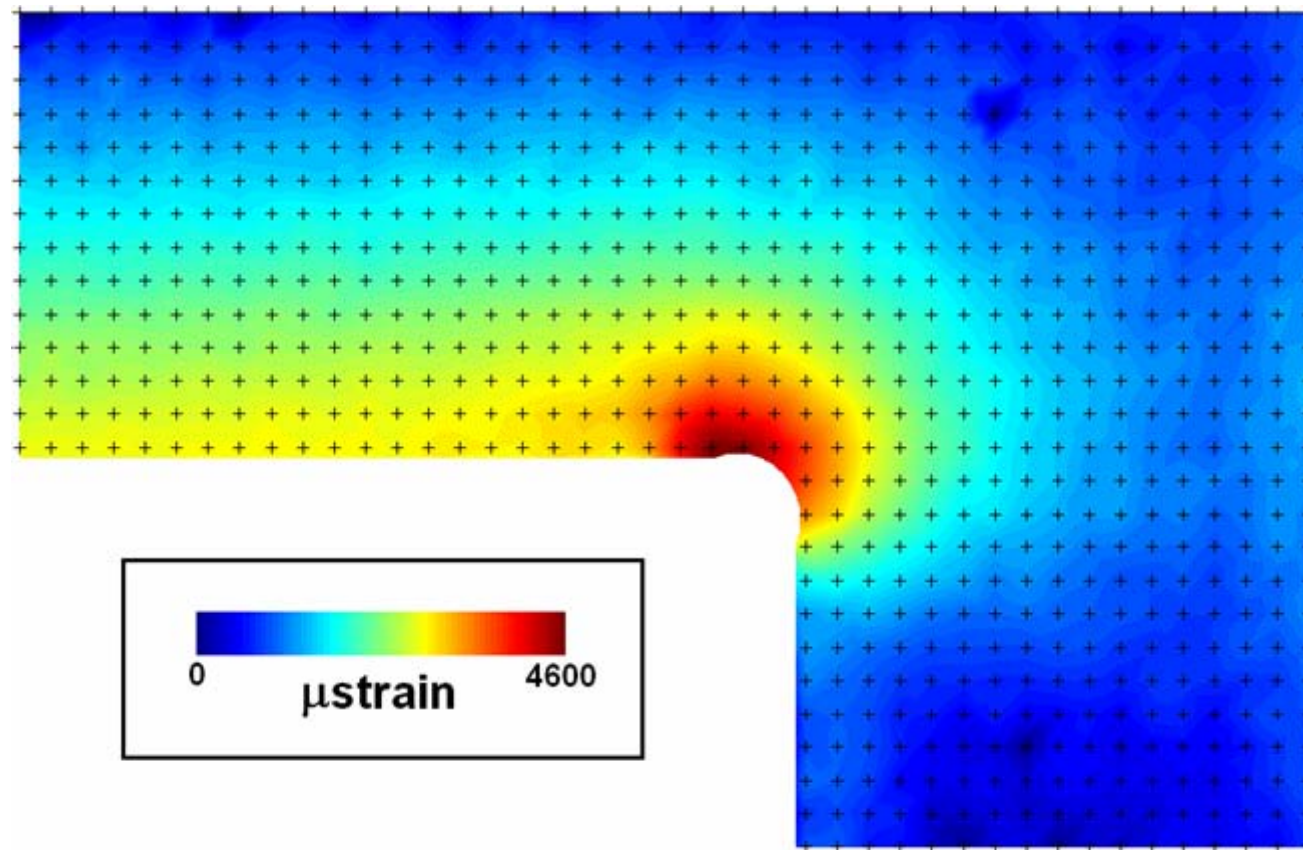
- 'A' is amplitude of spread and found using Matlab fitting routine.



# Measured strain map indicating mode shape



# Measured strain concentration around fillet

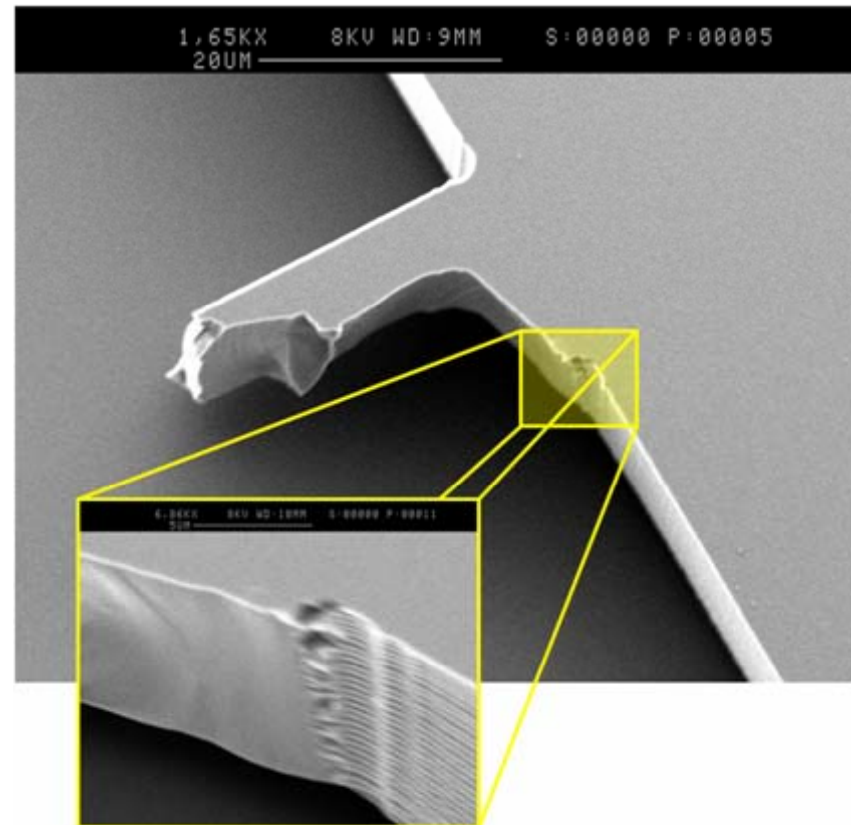


# Comparison of results

Technique	Freq. (KHz)	Vol. strain ( $\mu$ strain)	Comments
FEA	97.0	$8620 \pm 780$	Maximum
		$5360 \pm 490$	1 $\mu\text{m}^2$ average
Expt.	101.3	$4580 \pm 30$	1 $\mu\text{m}$ spot diameter

# Failure prediction

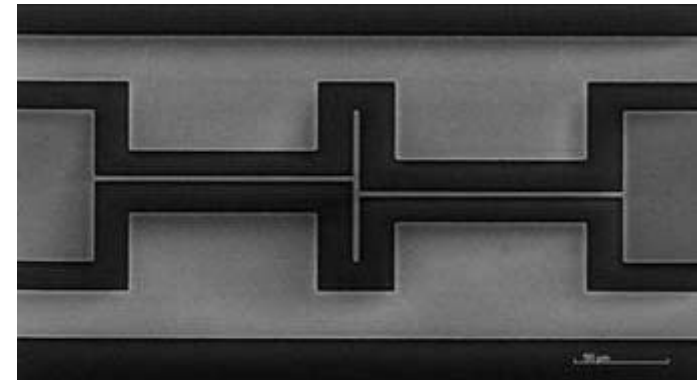
- Overdrive device to induce failure
- Crack initiates from high strain location
- Possible application to reliability studies



# Modelling material properties in NEMS

(B. Gallacher)

- Measure stress in Cu interconnect to aid IC reliability engineering
  - Static sensors
  - Dynamics sensors
- Investigating relaxation mechanisms in nanoscale thin films
- Using Off Lattice Kinetic Monte Carlo to determine critical thicknesses for:
  - Cracking
  - Dislocation



*Static device for Al*

# Summary - comparison of methods

Technique	Resolution	Range	Advantages
Profilometry	1nm	Static to <10 MHz	Large area
Vibrometry	10pm	10Hz to 20 MHz	FFT to determine all modes
Raman	30 $\mu$ strain	Unlimited	UHF and potentially high spatial resolution

# Personnel

- Mechanical Engineering:
  - Jim Burdess, John Hedley, Barry Gallacher
  - Zhongxu Hu, Michele Pozzi
- Electrical Engineering:
  - Alun Harris, Jeff Neasham

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